

(19) World Intellectual Property Organization
International Bureau



(43) International Publication Date
8 July 2010 (08.07.2010)

PCT

(10) International Publication Number
WO 2010/077500 A1

(51) International Patent Classification:
H01L 29/78 (2006.01) *H01L 21/336* (2006.01)

(21) International Application Number:
PCT/US2009/065856

(22) International Filing Date:
25 November 2009 (25.11.2009)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
61/120,818 8 December 2008 (08.12.2008) US
12/420,711 8 April 2009 (08.04.2009) US

(71) Applicant (for all designated States except US):
FAIRCHILD SEMICONDUCTOR CORPORATION
[US/US]; 82 Running Hill Road MS 35-4E, South Portland, Maine 04106-0022 (US).

(72) Inventors; and

(75) Inventors/Applicants (for US only): **YEDINAK, Joseph A.** [US/US]; 114 Ash Lane, Mountain Top, Pennsylvania 18707 (US). **PROBST, Dean E.** [US/US]; 6867 Liza Lane, West Jordan, Utah 84081 (US). **CHALLA, Ashok** [IN/US]; 10425 Zinnia Way, Sandy, Utah 84094 (US). **CALAFUT, Daniel** [US/US]; 108 Ballatore Court, San Jose, California 95134 (US).

(74) Agents: **YEAGER, Hal R.** et al.; Townsend and Townsend and Crew LLP, Two Embarcadero Center, 8th Floor, San Francisco, California 94111-3834 (US).

(81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PE, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, ST, SV, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MK, MT, NL, NO, PL, PT, RO, SE, SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:

- with international search report (Art. 21(3))
- before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments (Rule 48.2(h))

(54) Title: TRENCH-BASED POWER SEMICONDUCTOR DEVICES WITH INCREASED BREAKDOWN VOLTAGE CHARACTERISTICS

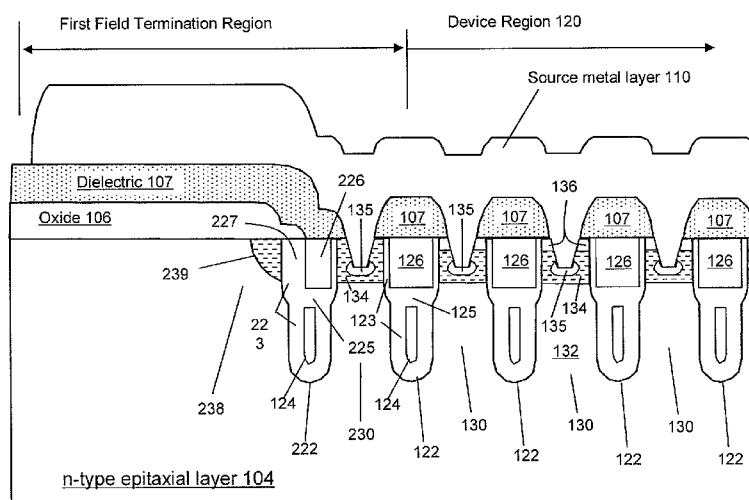


FIG. 5

(57) Abstract: Exemplary power semiconductor devices with features providing increased breakdown voltage and other benefits are disclosed.

TRENCH-BASED POWER SEMICONDUCTOR DEVICES WITH INCREASED BREAKDOWN VOLTAGE CHARACTERISTICS

CROSS-REFERENCES TO RELATED APPLICATIONS

- 5 **[0001]** This application claims the benefit of U.S. provisional patent application No. 61/120,818, filed December 8, 2008, which is incorporated herein by reference in its entirety for all purposes.

BACKGROUND OF THE INVENTION

- 10 **[0002]** Exemplary power semiconductor devices include planar-gate MOSFET transistors, vertical gate MOSFET transistors, insulated-gate bipolar transistors (IGBTs), rectifiers, and synchronous rectifiers. Typical implementations of the trench-gate variety of these devices comprise an array of trenches formed in the top surface of the semiconductor die, with each trench filled with a shield electrode and/or a gate electrode, depending upon the type of
- 15 power device. The trenches define a corresponding array of mesas, each mesa being disposed between adjacent trenches. Depending upon the device implemented on the die, various electrodes and/or doped regions are disposed at the top of the mesa. Each mesa and its adjacent trenches implement a small instance of the device, and the small instances are coupled together in parallel to provide the whole power semiconductor device. The whole
- 20 device has an ON state where a desired current flows through the device, an OFF state where current flow is substantially blocked in the device, and a breakdown state where an undesired current flows due to an excess off-state voltage being applied between the current conducting electrodes of the device. The voltage at which breakdown is initiated is called the breakdown voltage. Each mesa and its adjacent trenches are configured to provide a desired set of ON-
- 25 state characteristics and breakdown voltage. There are various tradeoffs in the design of the mesa and trenches between achieving good ON-state characteristics, high breakdown voltage, and improved switching characteristics.

- 30 **[0003]** A typical power semiconductor die has an active area where the array of mesas and trenches that implement the device are located, a field termination area around the active area, and an inactive area where interconnects and channel stops may be provided. The field termination area minimizes the electric fields around the active area, and is not intended to conduct current. Ideally, one would like the device's breakdown voltage to be determined by

the breakdown processes associated with the active area. However, there are various breakdown processes that can occur in the field termination area and inactive area at significantly lower voltages. These breakdown processes may be referred to as passive breakdown processes.

5 **[0004]** Much effort has been made in the prior art to design field termination areas that have higher breakdown voltages than the active area. However, such prior art designs often fall short of this goal, often requiring compromises that increase the total die area and cost of the die.

BRIEF SUMMARY OF THE INVENTION

[0005] The inventors have discovered several locations in trench-based power devices where parasitic breakdown conditions are likely to occur first. The present application provides novel and inventive features that counter these breakdown conditions and increase breakdown voltage.

15 **[0006]** Aspects of the exemplary embodiments of the present invention described herein
may be used alone or in any combination.

BRIEF DESCRIPTION OF THE DRAWINGS

[0007] FIG. 1 shows a top view of an exemplary semiconductor die that incorporates
20 several features according to the present invention.

[0008] FIG. 2 shows a magnified view of the left top corner of the exemplary semiconductor die of FIG. 1 according to the present invention.

[0009] FIG. 3 shows a magnified view of a portion of the left side of the exemplary semiconductor die of FIG. 1 according to the present invention.

25 **[0010]** FIGS. 4 and 5 show a first cross section view of a portion of the exemplary semiconductor die of FIG. 1 and a magnified view thereof in FIG. 5 according to the present invention.

[0011] FIG. 6 shows a magnified cross section view of a portion of a variation of the exemplary semiconductor die of FIG. 1 according to the present invention.

[0012] FIGS. 7-14 show various magnified cross section views of the exemplary semiconductor die of FIG. 1 and possible variations thereof according to the present invention.

[0013] FIG. 15 shows a top view of another exemplary semiconductor die that incorporates several features according to the present invention.

[0014] FIGS. 16-19 show various magnified cross section views of the exemplary semiconductor die of FIG. 15 and possible variations thereof according to the present invention.

[0015] FIG. 20 shows a top view of another exemplary semiconductor die that incorporates several features according to the present invention.

[0016] FIGS. 21-29 show various magnified cross section views of the exemplary semiconductor die of FIG. 20 and possible variations thereof according to the present invention.

[0017] FIG. 30 shows a top view of another exemplary semiconductor die that incorporates several features according to the present invention.

[0018] FIG. 31 show a magnified cross section view of the exemplary semiconductor die of FIG. 30 according to the present invention.

[0019] FIGS. 32-34 show various cross section views of an exemplary semiconductor die comprising a trench-shielded Schottky barrier diode device according to the present invention.

DETAILED DESCRIPTION OF THE INVENTION

[0020] The techniques in accordance with the present inventions will be described more fully hereinafter with reference to the accompanying drawings, in which exemplary embodiments of the invention are shown. This invention may, however, be embodied in different forms and should not be construed as limited to the embodiments set forth herein. Rather, these embodiments are provided so that this disclosure is thorough and complete and fully conveys the scope of the invention to one skilled in the art. In the drawings, the thicknesses of layers and regions may be exaggerated for clarity. The same reference numerals are used to denote the same elements throughout the specification. The elements may have different interrelationships and different positions for different embodiments.

[0021] It will also be understood that when a layer is referred to as being "on" another layer or substrate, it can be directly on the other layer or substrate, or intervening layers may also be present. It will also be understood that when an element, such as a layer, a region, or a substrate, is referred to as being "on," "connected to," "electrically connected to," "coupled to," or "electrically coupled to" another element, it may be directly on, connected or coupled to the other element, or one or more intervening elements may be present. In contrast, when an element is referred to as being "directly on," "directly connected to" or "directly coupled to" another element or layer, there are no intervening elements or layers present. It may be appreciated that the claims of the application may be amended to recite exemplary relationships described in the specification or shown in the figures with the support thereof being provided by the original application. The term "and/or" used herein includes any and all combinations of one or more of the associated listed items.

[0022] The terms used herein are for illustrative purposes of the present invention only and should not be construed to limit the meaning or the scope of the present invention. As used in this specification, a singular form may, unless definitely indicating a particular case in terms of the context, include a plural form. Also, the expressions "comprise" and/or "comprising" used in this specification neither define the mentioned shapes, numbers, steps, actions, operations, members, elements, and/or groups of these, nor exclude the presence or addition of one or more other different shapes, numbers, steps, operations, members, elements, and/or groups of these, or addition of these. Spatially relative terms, such as "over," "above," "upper," "under," "beneath," "below," "lower," and the like, may be used herein for ease of description to describe one element or feature's relationship to another element(s) or feature(s) as illustrated in the figures. It will be understood that the spatially relative terms are intended to encompass different orientations of the device in use or operation in addition to the orientation depicted in the figures. For example, if the device in the figures is turned over, elements described as "below" or "beneath" or "under" other elements or features would then be oriented "over" or "above" the other elements or features. Thus, the exemplary term "above" may encompass both an above and below orientation.

[0023] As used herein, terms such as "first," "second," *etc.* are used to describe various members, components, regions, layers, and/or portions. However, it is obvious that the members, components, regions, layers, and/or portions should not be defined by these terms. The terms are used only for distinguishing one member, component, region, layer, or portion from another member, component, region, layer, or portion. Thus, a first member, component, region, layer, or portion which will be described may also refer to a second

member, component, region, layer, or portion, without departing from the scope of the present invention.

[0024] FIG. 1 shows a top view of an exemplary semiconductor device **100** that incorporates several features according to the present invention. Device **100** comprises an active device region **120** located in the middle of the die. Without loss of generality, device region **120** may implement a vertical, trench-shielded power MOSFET device. As described and shown below in greater detail, the exemplary MOSFET device comprises an array of trenches interleaved with an array of mesas, insulated shield electrodes disposed in bottoms of the trenches, insulated gate electrodes disposed in the trenches over the shield electrodes, source regions disposed in the mesas, source electrodes disposed on the source regions, and a drain electrode provided at the backside of the semiconductor device. Device **100** further comprises a source metal layer **110** (also called conductive layer **110**) disposed over device region **120** and electrically coupled to the source electrodes, and a source pad **111** disposed over conductive layer **110** and electrically coupled thereto, and in turn to the source regions of the power MOSFET device. Source pad **111** is adapted to receive an external connection, such as a wire bond or solder bump that provides a source potential, and may have dimensions of 150 microns on each side.

[0025] On each of the left and right sides of the device region **120**, device **100** further comprises a connection region **150** where electrical contact is made to the gate and shield electrodes that are disposed in the trenches. In each connection region, a stripe of conductive material, called a gate runner, is disposed parallel to a side of device region **120** and spaced therefrom. The gate runner makes electrical contact with the gate electrodes in the trenches, but is electrically isolated from the mesas that are interleaved between the trenches. Each gate runner is electrically coupled to a gate pad **112** located at the bottom of the die. The gate pad **112** is adapted to receive an external connection, such as a wire bond or solder bump that provides a gate potential. Also in each connection region **150**, another stripe of conductive material, called a shield runner, is disposed parallel to the gate runner and spaced therefrom. The shield runner makes electrical contact with the shield electrodes in the trenches, but is electrically isolated from portions of the mesas that it overlies. The shield runners are electrically coupled to the source conductive layer by an extension of the source conductive layer at the top of the die, or to a shield pad and using an external connection.

[0026] A channel stopper is disposed at or near the periphery of the die, and is spaced from the shield runners and the top portion of device region **120** by a gap. The channel stopper is conventional, and may comprise an isolated ring of metal that overlays and makes contact to

a strip of doped semiconductor region that forms a ring around the periphery of the die. Of significant note, die **100** does not comprise the conventional field termination structures that would normally appear in this gap.

[0027] FIG. 2 shows a magnified view of the upper left-hand corner of die **100**, and FIG. 3 shows a magnified view of a portion along the left side of the die. The above features may be more clearly seen in these figures. FIGS. 2 and 3 provide reference points for a number of cross sections of die **100** that will be discussed next.

[0028] FIG. 4 is a cross section view of a portion of the die **100** that includes active device region **120** and a first field termination region. Die **100** comprises a N+ doped semiconductor substrate **102**, one or more epitaxially grown semiconductor n-type layers **104** (“epitaxial semiconductor layer”) disposed on semiconductor substrate **102**, an oxide layer **106** disposed over epitaxial semiconductor layer **104** in the inactive and first field termination regions, a dielectric layer **107** disposed over the oxide layer **106**, a gate runner disposed over the dielectric layer **107** at the left portion of the inactive region, and conductive layer **110** (source metal layer **110**) disposed over dielectric layer **107** in the first field termination region. As is known in the art, a semiconductor region may be doped as a p-conductivity type (or “p-type”) region with a p-type dopant, or doped as an n-conductivity type (or “n-type”) region with an n-type dopant. In device region **120**, device **100** further comprises a plurality of trenches **122** disposed in the epitaxial semiconductor layer, and a plurality of mesas **130** of semiconductor material interleaved between trenches **122**. Portions of the dielectric layer **107** cover the tops of trenches **122**, and the source metal layer **110** extends over active device region **120** and makes contact to mesas **130**. The structure of trenches **122** and mesas **130** is described below with reference to FIG. 5. In the first termination region, device **100** further comprises a first end trench **222**, a first end mesa **230** disposed between first end trench **222** and the leftmost trench **122** of device region **120**, and a second end mesa **238** disposed to the left of first end trench **222**.

[0029] FIG. 5 is a magnified cross section view of the first field termination region and device region **120** shown in FIG. 4. Each trench **122** has opposing sidewalls lined with a dielectric layer **123**, a shield electrode **124** disposed between the sidewalls near the bottom of the trench, a dielectric layer **125** disposed over shield electrode **124**, and a gate electrode **126** disposed over the dielectric layer and between the trench sidewalls. Each mesa **130** comprises a p-type well **134** disposed in the epitaxial semiconductor layer **104** adjacent to the top surface of layer **104**, a pair of source (n+ type) regions **136** disposed in p-well **134** adjacent to two adjacent trenches **122** and the top surface of the epitaxial semiconductor

layer **104**, and an N-drift region **132** disposed below p-well **134**. (A p-type well, a p-type region, and a p-doped region described herein may be referred to as “a well region of a first conductivity type” or “a well region of a second conductivity type”, depending upon the context of the discussion or the context of the claim.) A small trench is formed in the center of mesa **130** to allow the source metal layer **110** to make electrical contact to the source regions **136**, and to the p-well **134** at a small region **135** of enhanced p+ doping. Electron current is conducted vertically through the device, from source regions **136**, through an inverted region of the p-well **134** adjacent to the gate oxide **123**, further through drift region **132**, and down to the N+ substrate **102** and the drain contact, with the amount of current being modulated by the potential on the gate electrodes **126** in trenches **122** under normal operating conditions. The shield electrodes **124** are electrically coupled to the potential of the source metal layer **110** and source regions **136**, and shield the p-well from high electric fields.

[0030] When the potential on the gate electrode **126** is set to place the device in an off state (e.g., typically a potential of around zero volts), a substantial current can still flow during a breakdown condition where the drain potential is very high relative to the source potential. In the breakdown condition, high electric fields develop in a region in each mesa **130**, and this high electric field generates avalanche carriers (both holes and electrons). The voltage at which this breakdown condition occurs is called the breakdown voltage. The breakdown voltage of the mesa may be raised by selecting the shield oxide thickness, the width of the mesa, and the doping of the N-drift region **132** to cause the N-drift region **132** to be normally depleted of electrons. This causes the electric field during off-state conditions to be more uniformly distributed along the centerline of the mesa (e.g., a square-shaped electric field profile), thereby reducing the peak electric field (and thereby increasing the voltage at which avalanche carriers can be generated). The condition whereby the N-drift region **132** is depleted of electrons is called the “charge-balanced condition.” The charge-balanced condition can be generally achieved when the product of the mesa width and the doping of the N-drift region **132** is in the range of $1 \times 10^{11} \text{ cm}^{-2}$ to $1 \times 10^{13} \text{ cm}^{-2}$.

[0031] Ideally, one would like the breakdown voltage to be determined by the breakdown process associated with mesa **130**. However, various parasitic breakdown mechanisms occur in various field termination regions of the device at lower voltages, and thereby set the overall breakdown voltage of the device to a lower value than that caused by the breakdown process in mesa **130**. One such potential parasitic mechanism can occur at the thin portion of dielectric layer **123** in the outermost trench of a device region **120** designed with a

termination region of the prior art. Without a mesa **130** next to it, this thin dielectric layer would be exposed to the potential of the n-type epitaxial layer, which is coupled to the drain potential, and a large electric field can develop across the thin dielectric layer, which can cause a breakdown to occur at a relatively low voltage.

[0032] One feature according to the present invention addresses this parasitic breakdown mechanism by disposing an end trench **222** on either side of the array of active trenches **122** of the device region **120**. Trench **222** has opposing sidewalls lined with a dielectric layer **223**, a shield electrode **124** disposed between the sidewalls near the bottom the trench, a dielectric layer **125** disposed over shield electrode **124**, and a gate electrode **226** disposed over dielectric layer and between the trench sidewalls. However, unlike the dielectric layer **123** of trench **122**, dielectric layer **223** is thicker along the sidewall that faces the n-type epitaxial layer than along the side wall that faces the trenches **122** of device region **120**, as measured along the depth of gate electrode **226**. The thicker region is indicated by reference number **227** in the figure. The thicker dielectric reduces the electric field in the dielectric layer, and thereby increases its breakdown voltage. Trench **222** may have the same width as each of trenches **122**, and gate electrode **226** may have a smaller width than gate electrode **126**.

[0033] The above trenches **222**, **122** and mesas **238**, **230**, and **130** are indicated in the top plan view of FIG. 3 near the cross-section line indication for FIG. 4. A similar arrangement of trenches and mesas is present on the opposite side of device area **120**, as indicated by these reference numbers in the top plan view of FIG. 2. While the pair of trenches **222** bound the array of trenches **122** and mesa **130** on either side of the array (*e.g.*, the top and bottom of the array), they do not encircle the array or have portions that bound the right and left sides of the array. That is, there is no perpendicular termination trench at the ends of trenches **122** and mesas **130**. (It should be noted that trenches **122** and mesas **130** continue to run under the gate runner.) Related to this, device **100** does not have a p-doped region disposed at the ends of trenches **122**. Each of these features reduces the size of the field termination areas, and enables the active area to be increased and/or the die size to be decreased. While the above configuration is for a device region **120** that provides a MOSFET device, it can also apply to other device types, such as IGBT devices and rectifiers, particularly those devices in which the above-described charge-balanced condition exists.

[0034] Referring back to FIG. 5, as another feature of the present invention, the broad mesa **238** to the left of end trench **222** may optionally have a p-type region **239** disposed at its

surface, next to dielectric layer **223**. P-type region **239** may be directly decoupled from any potential, and left in a floating state, or may be electrically coupled to the source metal layer **110** and the source potential (*e.g.*, it may be grounded). In either case, region **239** reduces the electric fields around the top right corner of broad mesa **238**, to eliminate this area as a source of parasitic breakdown mechanism. When electrically coupled to the source potential, p-type region **239** further shields dielectric **223** from the drain potential in area **227**. P-type region **239** may be manufacturing during the same process that manufactures p-wells **134**.

[0035] As another feature of the present invention, the mesa **230** to the right of end trench **222** may be configured as a p-n diode rather than a MOSFET transistor. For this, it may comprise a p-well **134** and enhanced p+ doping region **135**, but no source regions **136**. The p-n diode is biased in an off state during normal operations of the MOSFET transistor of device region **120**. Mesa **230** provides additional spacing distance between broad mesa **238** and the first active mesa **130** that serves to buffer the potential in broad mesa **238** from the first active mesa **130**. This enables the electrical characteristics of the first mesa **130** to be substantially the same as the interior mesas **130**.

[0036] FIG. 6 shows a magnified cross section view of a portion of a variation of the exemplary semiconductor die of FIG. 1 according to the present invention. The features in the magnified cross section of FIG. 6 are the same as those shown in the magnified cross section of FIG. 5, with the addition of an additional end trench **220**, dielectric layer **221**, and shield electrode **124**. End trench **220** has opposing sidewalls lined with dielectric layer **221**, and a shield electrode **224** disposed between the sidewalls, preferably from the top of the epitaxial semiconductor layer to near the bottom of the trench. Shield electrode **224** is electrically coupled to the source metal layer **110**, or can be left electrically floating to assume a floating potential. Shield electrode **224** provides additional shielding of the drain potential for end trench **222** and gate electrode **226**. A mesa **230'** is defined between trenches **220** and **222**. P-doped region **239** may be included in mesa **230'** between trenches **220** and **222**, or omitted. Also, a p-doped region **234** that is disposed in mesa **230'** and that extends from trench **222** to trench **220** may be used. Along with region **234**, a p-doped region **239'** may be included on the left side of trench **220**. A pair of trenches **220** bound the array of trenches **122**, **222** and mesas **130**, **230**, **230'** on either side of the array (*e.g.*, the top and bottom of the array), but they do not encircle the array or have portions that bound the right and left sides of the array. This feature reduces the size of the field termination areas, and enables the active area to be increased and/or the die size to be decreased. While the above

configuration is for a device region **120** that provides a MOSFET device, it can also apply to other device types, such as IGBT devices and rectifiers, particularly those devices in which the above-described charge-balanced condition exists.

[0037] FIG. 7 shows a cross section view of the aforementioned trenches and mesas in connection area **150** just adjacent to the device area **120**, along the cut line 7-7 defined in FIG. 3. A thin amount of oxide layer **106** is disposed over each of mesas **130** and **230**, and dielectric layer **107** is disposed over gate electrodes **126** and **226**, as well as the underlying oxide layer **106**. The optional end trench **220**, shield electrode **221**, and dielectric layer **221** are shown in dotted outline. There is no change to the configuration of p-doped region **239** with respect to its neighboring elements with respect to the cross sections shown in FIGS. 4 and 5.

[0038] FIG. 8 shows a cross section view of the aforementioned trenches and mesas in connection area **150** under the gate runner, along the cut line 8-8 defined in FIG. 3. A thin amount of oxide layer **106** is disposed over each of mesas **130** and **230**. The tops of gate electrodes **126** and **226** are electrically coupled together by a conductive riser **126R**. Riser **126R** is electrically isolated from mesas **130**, **230** by thin portions of oxide **106**. In typical embodiments, riser **126R** and gate electrodes **126**, **226** are formed of the same material, such as polysilicon. In prior cross sections, the riser **126R** is removed. The metal gate runner makes contact to riser **126R** at locations over gate electrodes **126** and **226**, which are separated by islands of dielectric **107**. The islands may be omitted. The gate electrodes **126** and **226** terminate in the trenches at this point. The optional end trench **220**, shield electrode **221**, and dielectric layer **221** are shown in dotted outline. There is no change to the configuration of p-doped region **239** with respect to its neighboring elements with respect to the cross sections shown in FIGS. 4 and 5.

[0039] FIG. 9 shows a cross section view of the aforementioned trenches and mesas in connection area **150** between the gate runner and the shield runner, along the cut line 9-9 defined in FIG. 3. Only the shield electrodes **124** and **224** are present in trenches **122** and **222**, with oxide layer **106** covering them and the mesas **130** and **230**.

[0040] FIG. 10 shows a cross section view of a trench **122** in connection area **150** along a cut-line 10-10 defined in FIG. 3, with the cut-line 10-10 being perpendicular to cut lines 4-4, 7-7, 8-8, and 9-9. Gate electrode **126** and shield electrode **124** are disposed in the trench, with gate electrode **126** having a riser **126R** that makes electrical contact to the gate runner, and with shield electrode **124** having a riser portion **124R** that makes electrical contact to the

shield runner. Dielectric layer **125** is disposed between shield electrode **124** and gate electrode **126** along their facing horizontal dimensions, a dielectric layer **125S** is disposed between electrodes **124** and **126** along their facing side dimensions, and a corner patch **125C** of dielectric is disposed between the outside corner of gate electrode **126** and the inside corner of shield electrode **124**. Shield electrode **124** has an outside corner that is disposed adjacent to a patch **123C** of dielectric material, and a vertical side that is disposed adjacent to a side layer **123S** of dielectric material.

[0041] Radius of curvature effects significantly increase the electric fields in the regions next to the outside corners of shield electrode and gate electrode **126**. The thickness of dielectric patch **123C** is generally sufficient to prevent breakdown of the dielectric material. However, dielectric patch **125C** and dielectric side layer **125S** around gate electrode **126** are relatively thin, and can be a source of breakdown for the end trench **222** (shown in FIG. 8). The inclusion of optional shield electrode **224** and end trench **220** shields dielectric patch **125C** and dielectric side layer **125S** from the drain potential coupled to semiconductor layer **104**, and thereby reduces the electric fields in dielectric patch **125C** and dielectric side layer **125S**. Another possible area of breakdown due to radius of curvature effects, particularly for high voltage devices, is present in dielectric side layer **123S** at the end of shield riser portion **124R**, as indicated by point "A" in FIG. 10. This potential breakdown can be significantly mitigated by extending the topside shield runner metal (which is a conductive trace) over dielectric side layer **123S** and beyond the end of trench **122** by a distance **L1**. Distance **L1** may be equal to or greater than the depth of trench **122**. For lower voltage device applications, the possibility of breakdown at point "A" is very low, and the topside shield runner metal does not extend over dielectric side layer **123S** or beyond the end of trench **122**, as indicated by edge "B" in the figure. This configuration results in a thinner shield runner, and a smaller die.

[0042] FIG. 11 shows a cross section view of a mesa **130** in connection area **150** along a cut-line 11-11 defined in FIG. 3, with the cut-line 11-11 being perpendicular to cut lines 4-4, 7-7, 8-8, and 9-9. The p-doped well **134** and the riser **126R** for the gate electrodes **126** are shown at the right of the figure. Typically, p-doped well **134** is electrically coupled to the potential of the source and shield, but may be in a floating state for some instances where the region is used in a field termination area. P-doped well **134** has an end that terminates at or under gate riser **126R** (which is an electrical trace). For reference, the outlines of gate electrode **126** and shield electrode **124** are shown in dashed lines. There is a possibility of breakdown occurring at the end of p-doped well **134** due to radius of curvature effects.

However, the gate electrodes **126** and shield electrodes **124** that are disposed on either side of p-doped well **134** normally deplete the portion of n-doped mesa **130** that is adjacent to the end of well **134**, thereby significantly reducing the potential and electric fields around the end of well **134**. However, electric fields of reduced amounts are still present around the ends of well **134**, and can concentrate at the end of well **134** in a radial manner (*i.e.*, radius of curvature effect). However, with the configuration shown in FIG. 11, the end of well **134** is substantially shielded by gate riser **126R**, and substantially reduces the radius of curvature effects at the region's end. Specifically, conductive riser **126R** directs the electric fields present in mesa **130** at the end of well **134** away from the end of well **134** and towards itself, thereby reducing the radial concentration of the electric field. This shielding would be lost if the end of well **134** were to extend to the left side of the lower portion of conductive riser **126R**. This shielding effect is best obtained if the end of well **134** is spaced from the most distal side (*e.g.*, left side) of the lower portion of conductive riser **126R** by a distance **L2**, where **L2** is equal to or greater than the depth of well **134**. In preferred implementations, **L2** is equal to or greater than the depth of well **134** plus the separation distance between well **134** and conductive riser **126R**, where the separation distance is equal to the thin portion of oxide layer **106** for the configuration shown in the figure.

[0043] As mentioned above, the gate electrodes **126** and shield electrodes **124** that are disposed on either side of p-doped well **134** normally deplete the portion of the n-doped mesa **130** that is adjacent to the end of well **134**, thereby significantly reducing the potential and electric fields around the end of well **134**. To achieve this benefit, the end of p-doped region should be spaced from the ends of the shield electrodes **124**, or the ends of the trenches **122**, by at least a distance **L3**, as shown in FIG. 12. Distance **L3** may be equal to the depth of trench **122**, or may be equal to the difference between the depth of trench **122** and the depth of well **134**. It is possible for well **134** to extend beyond gate riser **126R**, as is shown in FIG. 13, and further possible for the end of well **134** to be disposed under the shield runner (and field plate). If the shield runner is disposed near or over the end of well **134**, it can provide shielding to mitigate the radius of curvature effects at the end of well **134** in the same manner that gate riser **126R** provided shielding, as previously described with reference to FIG. 11. However, for low and moderate voltage applications, the shield runner need not be disposed over the end of p-doped well **134**. While it is preferable that no other p-doped regions are disposed between the end of well **134** and the ends of the adjacent trenches, a more lightly p-doped region may be disposed between the end of well **134** and the ends of the adjacent trenches. The more lightly p-doped region has a lower dopant dose, as measured

across a cross section of the mesa width, than that of well **134**. Said another way, the more lightly p-doped region has a lower integrated charge resulting from the dopant, as measured across a cross section of the mesa width, than that of well **134**. With the above configurations, there is no need for a termination trench running perpendicular to the ends of trenches **122**, as would be done in prior art configuration. All of the above configurations of the end of p-doped well **134** may be applied to trench-shielded Schottky barrier diode devices, where the above spacing distances are applied to the end of the Schottky metal, or if a p-doped region like region **239'** shown in FIG. 6 is used around the perimeter of the Schottky metal. An exemplary embodiment of a trench-shielded Schottky barrier diode device employing these inventive aspects is described below with reference to FIGS. 32-34.

[0044] Referring back to FIG. 10, it may be seen that the shield runner metal makes electrical contact with a top surface of the riser portion **124R** of shield electrode **124** at a level that is at or below the top surface of epitaxial layer **104**. This feature is also shown in FIG. 14, which is a cross section that is perpendicular to the cross section of FIG. 10. As seen in FIG. 14, the contacts from the shield runner metal to the riser portions **124R** are made through contact openings formed through dielectric layer **107** and oxide layer **106**. This configuration has the advantages of reduced electrical contact resistance, and a simplification of the manufacturing process. In the conventional manufacturing processes, a polysilicon etch mask and etching step are used to define a polysilicon bus structure between the shield runner metal and the shield electrodes **124**, **224**. However, the above simplified contact structure can be defined by modifying an earlier mask that is used in the process, such as the mask used to define the contacts from the source metal to enhanced doping regions **135** and source regions **136** shown in FIG. 5. Accordingly, the mask and etching step that are conventionally used to define the above-described polysilicon bus structure may be eliminated.

[0045] When making a high current capacity device, several instances of device region **120** may be used rather than one large device region **120**. The instances of device region **120** are electrically coupled in parallel, and this configuration provides a low-resistance path to the centers of the shield electrodes **124** and the centers of the gate electrodes **126** compared to the case where one large instance of device regions **120** is used. FIG. 15 shows a top schematic plan view of a semiconductor device **200** disposed on a semiconductor die. Device **200** comprises a top device region **120A** disposed over a bottom device region **120B**, a top connection region **150** (as previously described above) disposed above top device region **120A**, a bottom connection region **150** disposed below device region **120B**, a middle

connection region **250** disposed between device regions **120A** and **120B**. Device regions **120A** and **120B** are instances of previously-described device region **120**. There is a gate runner and shield runner in each connection region **150**, and two gate runners and one shield runner in middle connection region **250**. The gate runners are electrically coupled to a gate pad **212** by a gate feed. Source metal layer **110** is disposed over device regions **120A** and **120B**, an electrically coupled to the shield runners and two source pads **111**. A plurality of interleaved trenches **122'** and mesas **130'** are disposed in the semiconductor epitaxial layer, and within the device regions **120A**, **120B** and connection regions **150**, **250**, as illustrated by the dashed lines at the right side of the figure. Only the first few trenches and mesas are shown for visual clarity in the figure, but the arrow symbols to the left of the array schematically indicate that the array of interleaved trenches and mesas extends to the left sides of the device regions **120A**, **120B** and connection regions **150**, **250**. Trenches **122'** are substantially the same as trenches **122**, except they run continuously through device regions **120A**, **120B** and connection regions **150**, **250**. Mesas **130'** are substantially the same as mesas **130**, except they run continuously through device regions **120A**, **120B** and connection regions **150**, **250**. A channel stopper structure surrounds regions **120A**, **120B**, **150**, and **250** at the perimeter of the die, and is separated from regions **120A**, **120B**, **150**, and **250** by a gap. This gap is the same as the gap shown and identified in FIG. 11.

[0046] FIG. 16 shows a cross sectional view of connection region **250** along the cut line 16-16 shown in FIG. 15. The cross section is taken along a trench **122'**. The components are the same as the components described above with reference to FIG. 10, with the exceptions that a mirror set of a gate electrode **126**, gate riser **126R**, and gate runner appear at the left side of the figure, that the dielectric patch **123C** and dielectric side **123S** are not present, and that trench **122'**, dielectric layer **123'**, shield electrode **124'**, and shield riser **124R'** are mirrored over to the left side and run continuously along the cross section from left to right. The gate runners make electrical contact to the gate risers **126R** of the gate electrodes **126**, but are electrically insulated from the shield metal runner and the shield riser **124R'** and the shield electrode **124'**. The shield runner metal makes electrical contact to the shield riser **124R'** and shield electrode **124'**, and is electrically insulated from the gate runners, gate risers **124R**, and gate electrodes **124**. The above trench construction eliminates the imbalances in the electric fields and potentials that occur in the mesa regions of device **100** that are next to the trench discontinuities in connection regions **150**, and thus eliminate the corresponding localized charge imbalances. This construction is a departure from prior art

constructions, which would include elaborate field termination structures in the middle of connection region **250**.

[0047] FIG. 17 shows a cross sectional view of connection region **250** along the cut line 17-17 shown in FIG. 15. The cross section is taken along a mesa **130'**. The components are the same as the components described above with reference to FIG. 10, with the exception that a mirror set of a p-doped well **134**, a gate electrode **126**, a gate riser **126R**, and a gate runner appear at the left side of the figure. Outlines of the positions of shield electrode **124'** and gate electrodes **126** are shown in dashed lines. Similar to device **100**, each p-doped well **134** is typically electrically coupled to the potential of the source and shield, but may be in a floating state for some instances where the region is used in a field termination area. Each p-doped well **134** has an end that preferably terminates at or under a respective gate conductive riser **126R** (which is an electrical trace). There is a possibility of breakdown occurring at the end of each p-doped well **134** due to radius of curvature effects. However, the gate electrodes **126** and shield electrodes **124** that are disposed on either side of the p-doped well **134** normally deplete the portion of each n-doped mesa **130** that is adjacent to the end of the well **134**, thereby significantly reducing the potential and electric fields around the end of the well **134**. However, electric fields of reduced amounts are still present around the ends of the well **134**, and can concentrate at the end of the well **134** in a radial manner (*i.e.*, radius of curvature effect). However, with the configuration shown in FIG. 17, the ends of the wells **134** are substantially shielded by the gate conductive risers **126R**, and the configuration substantially reduces the radius of curvature effects at the regions' ends (as previously described above for device **100** with reference to FIG. 11). This shielding would be lost if the end of a well **134** were to extend beyond the distal side of the lower portion of the conductive riser **126R** disposed above it. This shielding effect is best obtained if the end of the well **134** does not extend beyond the distal side of the lower portion of the conductive riser **126R**, and is further spaced from the most distal side of the lower portion of conductive riser **126R** by a distance **L2**, where **L2** is equal to or greater than the depth of well **134**. In preferred implementations, **L2** is equal to or greater than the depth of well **134** plus the separation distance between well **134** and conductive riser **126R**, where the separation distance is equal to the thin portion of oxide layer **106** for the configuration shown in the figure.

[0048] FIG. 18 shows a cross sectional view of a variation **250'** of connection region **250** that includes an electrically floating p-doped well **134C** disposed in epi layer **104**, and under the shield runner metal. (The p-doped region is made floating by not making a direct

electrically connection between it and a conductive layer that is adapted to receive an electrical potential from an external circuit.) The floating p-doped well **134C** acts as a buffer shield between epi layer **104** and the portion of the oxide layer **106** above it. The portion of oxide layer **106** between the shield runner metal and epi layer **104** can experience high electric fields since the shield runner metal is usually at ground potential and the underlying portion of epi layer **104** is usually at the drain potential. To reduce radius of curvature effects at the ends of p-doped well **134C**, the ends may be disposed near or under the gate risers **126R**.

[0049] FIG. 19 shows a cross sectional view of another variation **250''** of connection region **250** that includes a continuous p-doped well **134'** in place of the two wells **134** shown in FIG. 17. Continuous p-doped well **134'** extends from device region **120A** to device region **120B**, and through connection region **250''**, and is electrically coupled to the source metal layer **110** (and, in turn, to the shield runner metal). There is no radius of curvature effect associated with continuous p-doped well **134'** because well **134'** does not have a side edge or corner. Continuous p-doped well **134'** also acts as a buffer shield between epi layer **104** and the oxide layer **106** above it. As indicated above, the portion of oxide layer **106** between the shield runner metal and epi layer **104** can experience high electric fields since the shield runner metal is usually at ground potential and the underlying portion of epi layer **104** is usually at the drain potential.

[0050] In all of the embodiments illustrating connection regions **150**, **250**, **250'**, and **250''**, it may be appreciated that each connection region has a configuration of one more material bodies with the adjacent portions of mesas **130**, **130'** which produces an inactive device. A material body may comprise a doped region, a dielectric layer, a conductive layer, *etc.* In contrast, each device region **120**, **120A**, **120B** has a configuration of one more material bodies with portions of the mesas **130**, **130'** which produces an active device.

[0051] Another embodiment is now described and illustrated with reference to semiconductor device **300** illustrated in FIG. 20. Semiconductor device **300** has substantially the same floor plan (top plan view) as semiconductor device **100** shown in FIGS. 1-3. FIG. 20 is a magnified view of a portion along the left side of the die of semiconductor device **300**, similar to the magnified view of the left side portion of device **100** shown in FIG. 3. Semiconductor device **300** comprises substantially the same elements as device **100** arranged in substantially the same way, and further comprises a perimeter trench **320** that encircles the entire array of trenches **122,222** and mesas **130,230** previously described above, or a encircles at least 75% of the perimeter around the array. (It may be appreciated that

perimeter trench **320** may be discontinuous with one or more breaks of relatively small breaks, which may not significantly affect its effects.) FIGS. 21 and 22 shows cross sections of perimeter trench **320** and the array of trenches **122,222** and mesas **130,230** along the bottom of the array, and along the cut lines 21-21 and 22-22 shown in FIG. 20. Perimeter trench **320** comprises a dielectric layer **321** lining its opposing side walls, and a conductive electrode **324** disposed in the trench. Conductive electrode **324** may be electrically coupled to a conductive layer, such as the shield runner, to receive a ground potential, or may be decoupled from any conductive layer bearing a potential, thereby being at a floating potential. Perimeter shield **320** is spaced from trench **222** by a distance that is on the order of the spacing between adjacent trenches **122**. A gap region **330** is disposed between perimeter shield **320** and trench **222**. No electrical potentials are coupled to the top of gap region **330** by any conductive layer, and the potential in gap region **330** is floating. When the perimeter trench electrode **324** is at a floating potential, the potentials on it and the floating gap region **330** can float to set equalizing potentials with respect to the drain potential, and can thereby reduce sensitivity to charge imbalances in gap region **330**. As a result, achieving the charge balance condition in gap region **330** becomes easier than if these gap regions **330** were fixed at source potential by conventional grounded p-wells. Substantially the same benefits are achieved when the perimeter trench electrode **324** is coupled to a ground potential. The width of gap region **330** may be equal to or less than 1.25 times the width of mesa **130**, and the widths of gap region **330** along the various sides of perimeter trench **320** may be different. For example, the width of gap region **330** along the left and right vertical sides of perimeter trench **320** (and the main array of trenches **122** and mesas **130**) may be smaller than the width of gap region **330** along the top and bottom horizontal sides of perimeter trench **320** (and the main array).

[0052] FIGS. 23 and 24 are cross sections showing perimeter trench **320** along the ends of the primary trenches **122** and mesas **130**, and along the cut lines 23-23 and 24-24 shown in FIG. 20. The cross-sections of FIGS. 23 and 24 are substantially the same as the cross sections of FIGS. 10 and 11 for device **100**, plus the addition of perimeter trench **320** and gap region **330**. Elements **102-107, 120, 122, 123, 123C, 123S, 124, 124R, 125, 125C, 125S, 126, 126R, 134, 150**, the shield runner, the gate runner, and channel stopper have their same relative relationships with respect to one another. As indicated above, one possible area of breakdown due to radius of curvature effects, particularly for high voltage devices, is present in dielectric side layer **123S** at the end of shield riser portion **124R**, as indicated by point "A" in FIG. 23 (the same as was for FIG. 10). As previously described, this possible area of

breakdown can be significantly mitigated by extending the topside shield runner metal (which is a conductive trace) over dielectric side layer **123S** and beyond the end of trench **122** by a distance **L1**. Distance **L1** may be equal to or greater than the depth of trench **122**. Perimeter trench **320** also mitigates the possible area of breakdown by moving electric fields away from point A. As indicated above, when the perimeter trench electrode **324** is at a floating potential, the potentials on it and the floating gap region **330** can float to set equalizing potentials with respect to the drain potential, and can thereby reduce sensitivity to charge imbalances in gap region **330**. As a result, achieving the charge balance condition in gap region **330** becomes easier than if these gap regions **330** were fixed at source potential by the conventional grounded p-doped wells. Substantially the same benefits are achieved when the perimeter trench electrode **324** is coupled to a ground potential, which may be done by a contact via **325** of conductive material disposed between shield electrode **324** and the shield runner metal, with the conductive contact via **325** being electrically coupled to both the shield runner and shield electrode **324**.

[0053] The same above benefits can be substantially achieved with the use of a floating p-doped well **334** in floating gap region **330**. This embodiment is illustrated by FIGS. 25-28, which are the same cross-sections as FIGS. 21-24, with the exception of the addition of the floating p-doped well **334**. No ground potential voltage is coupled to well **334**. FIG. 29 shows floating p-doped well **334** in the portion of gap region **330** that is disposed between trench **222** and the perimeter trench **320**. Well **334** extends left to be adjacent to perimeter trench **320**. While well **334** has been shown as a continuous stripe that is disposed adjacent to perimeter trench **320**, it may be appreciated that well **334** may be segmented (having gaps in the continuous stripe). The ends of any segmented region of well **334** may be disposed under a shield runner and other conductive traces to minimizing radius of curvature effects.

[0054] As indicated above, perimeter trench **320** may be continuous and encircle the entire array of trenches **122,222** and mesas **130,230**, or may be discontinuous and encircle at least 75% of the perimeter around the array. Referring back to FIG. 20, when using a discontinuous perimeter trench **320**, breaks in trench **320** are typically introduced at the corners of the array, with each break typically being less than twice the width of gap region **330**, and typically equal to the width of the gap region **330**. In one embodiment using a discontinuous perimeter trench **320**, the perimeter trench is broken at the end of its horizontal legs at point "D" in FIG. 20 so that the horizontal legs of perimeter trench **320** have the same length as the interior trenches **122, 222**. The vertical legs of perimeter trench **320** may end flush with the ends of the horizontal legs, or may extend beyond the ends

of the horizontal legs, as shown by the dashed extension of one of the vertical legs to point “E” in FIG. 20. The latter extensions are currently preferred over ending the vertical legs flush with the ends of the horizontal legs. In another embodiment using a discontinuous perimeter trench 320, the perimeter trench is broken at the end of its vertical legs at point “F” in FIG. 20 so that the horizontal legs of perimeter trench 320 extend beyond the ends of the interior trenches 122, 222. The horizontal legs of perimeter trench 320 may end flush with the ends of the vertical legs, or may extend beyond the ends of the vertical legs in the same manner as described in the previous embodiment. In each of the previous two embodiments, the horizontal legs and vertical legs of the perimeter trench 320 may be electrically floating or ground. It is possible to have the vertical legs electrically grounded while having the horizontal legs electrically floating, or *vice versa*. As such, different segments of a discontinuous perimeter trench 320 may have different electrical states (e.g., floating state, grounded state).

[0055] When using perimeter trench 320, either with a grounded or floating electrode 324, there can be a charge imbalance at the corner turns of perimeter trench 320. This is because gap region 330 sees two sides of perimeter trench 320 instead of one, as shown in the magnified top plan view of FIG. 30. The electrode 324 of the perimeter trench tries to deplete more charge than that present in the corner area of gap region 330. This charge imbalance can be addressed by shortening the length of trench 222 that is adjacent to the horizontal leg of perimeter trench 320. This presented as device 400, which is the same as device 300 except for the shortening of the trench. The shortening of trench 222 reduces the charge imaging effect of trench 222 on the corner of gap region 330, and thereby compensates for the over imaging of electrode 324 of the perimeter trench. FIG. 31 shows a cross section of shortened trench 222, along with an outline of the un-shortened length for comparison. The end of trench 222 is spaced further from perimeter trench 320 than the ends of trenches 122. The p-well 334 of device 300 may be added to device 400, with any of the above-described configurations of device 400. The p-well 334 for device 400 may be at a floating potential or at a fixed potential (e.g., ground potential).

[0056] As briefly indicated in the discussion of device 100 and FIGS. 1-14, some inventive aspects of device 100 may be applied to trench-shielded Schottky barrier diode devices. A Schottky diode device may have a similar construction as device 100, as illustrated in FIGS. 1-14, and may include the same components as device 100 but without the need for gate electrodes 126 and 226, gate runners, gate pads, source regions 136, the portions of dielectric layers 106 and 107 disposed over the mesas, and well regions 134. FIGS. 32-34

show cross sections of an exemplary Schottky diode device **100''** according to aspects of the present invention. FIG. 32 shows a cross section through the device region **120** of device **100''** similar to the cross section shown in FIG. 6 for device **100**. Device **100''**

comprises trenches **122''** and **222''** that are similar to trenches **122** and **222**, respectively,

except that trenches **122''** and **222''** need not comprise gate electrodes **126** and **226**,

respectively, and may comprise shield electrodes **124''** that extend to the top of epitaxial

layer **104**, or near thereto, and which are taller than shield electrodes **124**. (In other Schottky embodiments, gate electrodes **126** and **226**, along with the gate runners, may be used, in which case they are typically coupled to the potential of the source metal layer **110**.)

Device **100''** also comprises trench **220**, mesas **130**, **230**, and **230'**, dielectric layer **106** and

107 in the field termination regions, and source metal layer **110** of device **100**. As a difference with device **100**, the source metal layer and the shield runner may be merged together as there is not gate runner between them. Source metal layer **110** contacts the tops

of mesas **130** to provide Schottky barrier contacts therewith. A surface compensation implant

may be disposed at the tops of mesas **130** to adjust the electrical characteristics (*e.g.*, barrier height) of the Schottky contacts, as is known to do in the art. A p-type well **134''** may be

disposed at the top of mesa **230** to provide a p-n junction diode having a higher reverse-bias breakdown voltage than the Schottky barrier devices in mesas **130**. Well **134''** may have a higher doping than well **134'** so that enhanced doping region **135** may be omitted, or

enhanced doping region **135**, or a layer of enhanced doping at the top of mesa **230**, may be included to provide a good conductive connection with source metal layer **110**. In another

implementation of device **100**, well **134''** may be omitted, and dielectric layers **107** and/or **106** may be extended over the top of mesa **230** to electrically insulate it from source metal

layer **110**, thus making it like mesa **230'**. In each of the implementations for mesa **230**,

mesa **230** and trenches **222''** and **122''** serve to shape the electric potential and field patterns as described above for device **100** to improve the overall breakdown voltage characteristics of device **100''**.

[0057] FIG. 33 shows a cross section of a trench **122''** in connection area **150** along a cut-line 10-10 defined in FIG. 3. The cross section of FIG. 33 is similar to the cross section

shown in FIG. 10 for device **100**. Shield electrode **124''** is disposed in the trench, with shield electrode **124** making electrical contact to the shield runner and source metal layer **110**.

Shield electrode **124''** has an outside corner that is disposed adjacent to a patch **123C** of dielectric material, and a vertical side that is disposed adjacent to a side layer **123S** of

dielectric material. As previously described, radius of curvature effects significantly increase

the electric fields in the regions next to the outside corners of shield electrode. A possible area of breakdown due to radius of curvature effects, particularly for high voltage devices, is present in dielectric side layer **123S** at the end of shield electrode **124''**, as indicated by point "A" in FIG. 33. This potential breakdown can be significantly mitigated by extending the topside shield runner metal (which is a conductive trace) over dielectric side layer **123S** and beyond the end of trench **122''** by a distance **L1**. Distance **L1** may be equal to or greater than the depth of trench **122''**. For lower voltage device applications, the possibility of breakdown at point "A" is very low, and the topside shield runner metal need not extend over dielectric side layer **123S** or beyond the end of trench **122''**, as indicated by edge "B" in the figure. This configuration results in a thinner shield runner, and a smaller die.

[0058] FIG. 34 shows a cross section of a mesa **130** in connection area **150** of device **100''** along a cut-line 11-11 defined in FIG. 3. This cross section is similar to the cross sections shown in FIGS. 11-13 for device **100**. As shown in FIG. 34, source metal **110** covers a portion of the top of mesa **130** (shown at the right in the figure) to provide the Schottky barrier contact. The location of the shield electrodes **124''** on either side of the mesa **130** are shown in dashed outlines. Dielectric layers **106** and **107** separate the shield runner and field plate from the mesa. There is a possibility of breakdown occurring at the end edge of the source metal layer **110**, where it contacts mesa **130**, due to radius of curvature effects. This end edge is the end of the Schottky barrier metal (*i.e.*, that part of the metal that forms a Schottky barrier with the semiconductor), and is indicated as point "C" in the figure. The shield electrodes **124''** that are disposed on either side of mesa **130** normally deplete the portion of the mesa that is adjacent to the end edge of source metal layer **110**, thereby significantly reducing the potential and electric fields around the end edge. To achieve this benefit, the end edge should be spaced from the ends of the shield electrodes **124''**, or the ends of the trenches **122''**, by at least a distance **L3**, as shown in FIG. 34. Distance **L3** may be equal to the depth of trench **122''**. With this configuration, there is no need to dispose a p-doped region in mesa **130** at the end edge of the Schottky barrier metal at point C, as may be done in prior art configurations. However, a p-doped region may be disposed in mesa **130** near the end edge of the Schottky barrier metal, as indicated by the dashed outline of a p-doped region **334'**. If p-doped region **334'** is used, it should be spaced from the ends of the shield electrodes **124''**, or the ends of the trenches **122''**, by at least the above distance **L3**.

[0059] As can be seen in each of FIGS. 33 and 34, there is no perpendicular termination trench disposed at the top surface of layer **104**, perpendicular to the ends of trenches **122''** and shield electrode **124''**. This is the same termination configuration as that shown above

for device **100**, and reduces the die size. However, if desired, a perpendicular termination trench or a perimeter trench may be added to device **100**".

[0060] While the above embodiments have been illustrated with n-type epi layers and p-type doped well regions, it may be appreciated that the inventions and embodiments may be practiced with p-type epi layers and n-type doped well regions. In other words, the inventions and embodiments may be practiced with the doping polarities of the layers and regions reversed.

[0061] While the various embodiments of the inventions are mostly described in the context of N-channel shielded gate MOSFET, these embodiments may be implemented in a variety of other types of devices, such as, P-channel MOSFET (*i.e.*, a transistor similar in structure to the MOSFETs described above except that the conductivity type of all silicon regions are reversed); N-channel shielded gate IGBT (*i.e.*, a transistor similar in structure to the MOSFETs described above except that a P-type substrate is used instead of the N-type substrate); P-channel shielded gate IGBT (*i.e.*, a transistor similar in structure to the MOSFETs described above but with silicon regions of opposite conductivity except the substrate is kept N-type); shielded gate synchronous rectifiers (*i.e.*, integrated shielded gate MOSFET and Schottky); TMBS rectifiers, and superjunction variations of the above devices (*i.e.*, devices with columns of alternating conductivity type silicon).

[0062] Any recitation of "a", "an", and "the" is intended to mean one or more unless specifically indicated to the contrary.

[0063] The terms and expressions which have been employed herein are used as terms of description and not of limitation, and there is no intention in the use of such terms and expressions of excluding equivalents of the features shown and described, it being recognized that various modifications are possible within the scope of the invention claimed.

[0064] Moreover, one or more features of one or more embodiments of the inventions may be combined with one or more features of other embodiments of the invention without departing from the scope of the invention.

[0065] While the present inventions have been particularly described with respect to the illustrated embodiments, it will be appreciated that various alterations, modifications, adaptations, and equivalent arrangements may be made based on the present disclosure, and are intended to be within the scope of the invention and the appended claims.

WHAT IS CLAIMED IS:

1. A semiconductor device comprising:
 - a first trench extending into a semiconductor region;
 - a first dielectric layer lining opposing sidewalls of the first trench, the first dielectric layer being thicker along one of the opposing sidewalls than along the other;
 - a gate electrode disposed in the first trench; and
 - a plurality of trenches extending into the semiconductor region, each of the plurality of trenches having opposing sidewalls lined with a dielectric layer and a gate electrode disposed between the sidewalls, the dielectric layer of each trench having the same thickness along the portions of both the opposing sidewalls that face the gate electrode.
2. The semiconductor device of claim 1 wherein the first trench and the plurality of trenches have the same width.
3. The semiconductor device of claim 1 wherein the gate electrode in the first trench has a smaller width than the gate electrode in each of the plurality of trenches.
4. The semiconductor device of claim 1 further comprising:
 - well regions of a first conductivity type extending in the semiconductor region between each pair of adjacent trenches; and
 - source regions of a second conductivity type disposed in the well regions adjacent each of the opposing sidewalls of each of the plurality of trenches; and
 - wherein the first trench does not have a source region disposed adjacent at least one of its opposing sidewalls.
5. The semiconductor device of claim 1 further comprising:
 - a second trench extending into the semiconductor region;
 - a second dielectric layer lining opposing sidewalls of the second trench, the second dielectric layer being thicker along one of the opposing sidewalls of the second trench than along the other; and
 - a gate electrode disposed in the second trench; and
 - wherein the first and second trenches and the plurality of trenches are all stripe-shaped, and the plurality of trenches are disposed between the first and second trenches.

6. The semiconductor device of Claim 1, wherein the plurality of trenches are disposed to a first side of the first trench, and wherein the semiconductor device further comprising a second trench disposed to a second side of the first trench, the second trench having a first side wall, a second side wall, a conductive body disposed between the side walls.

7. The semiconductor device of Claim 6, further comprising a well region of a first conductivity type disposed in the semiconductor layer and between the first and second trenches.

8. The semiconductor device of Claim 6 wherein the conductive body of the second trench is electrically floating.

9. The semiconductor device of Claim 6 wherein the conductive body of the second trench is electrically coupled to a conductive layer to receive a potential.

10. A semiconductor device comprising:
a plurality of parallel trenches extending in a semiconductor region, each trench having a shield electrode and a gate electrode vertically stacked therein, the gate and shield electrodes being insulated from each other; and
wherein the plurality of parallel trenches are bounded on two sides by two end trenches that extend in parallel with the plurality of trenches but do not encircle the plurality of the trenches.

11. The semiconductor device of Claim 10, wherein the device does not have a well region of a first conductivity type disposed at the ends of the parallel trenches.

12. The semiconductor device of Claim 10, wherein the semiconductor device comprises a MOSFET structure or an IGBT structure.

13. The semiconductor device of Claim 10, further comprising a plurality of mesas disposed between the trenches, each mesa having a width between adjacent trenches and an n-doped drift region, wherein the product of the mesa width and the doping of the mesa's drift region is in the range of $1 \times 10^{11} \text{ cm}^{-2}$ to $1 \times 10^{13} \text{ cm}^{-2}$.

14. A semiconductor device disposed on a semiconductor die, the semiconductor device comprising:

a semiconductor layer disposed on the die and having a first surface and a second surface;

a first trench disposed at the first surface of the semiconductor layer and having a first end facing a first edge of the semiconductor die, and a second end;

a second trench disposed at the first surface of the semiconductor layer and having a first end adjacent to the first end of the first trench and facing the first edge of the semiconductor die, and a second end;

a gate electrode disposed in the first and second trenches; and

a first portion of the semiconductor layer disposed between the first ends of the first and second trenches and the first edge of the semiconductor die; and

wherein the first portion does not have a perpendicular termination trench disposed at the first surface of the semiconductor layer.

15. The semiconductor device of Claim 14 wherein the first portion does not have a well region of a first conductivity type disposed between the first and second trenches.

16. The semiconductor device of Claim 14, further comprising a mesa disposed between the first and second trenches, the mesa having a width between the trenches and an n-doped drift region, wherein the product of the mesa width and the doping of the mesa's drift region is in the range of $1 \times 10^{11} \text{ cm}^{-2}$ to $1 \times 10^{13} \text{ cm}^{-2}$.

17. A trench shielded Schottky barrier rectifier semiconductor device comprising:

a semiconductor layer disposed on the die and having a first surface and a second surface;

a first trench disposed at the first surface of the semiconductor layer and having a first end facing a first edge of the semiconductor die, and a second end;

a second trench disposed at the first surface of the semiconductor layer and having a first end adjacent to the first end of the first trench and facing the first edge of the semiconductor die, and a second end;

a shield electrode disposed in the first and second trenches; and

a first portion of the semiconductor layer disposed between the first ends of the first and second trenches and the first edge of the semiconductor die; and

a Schottky barrier metal disposed between the first and second trenches, and between the trench ends; and

wherein the first portion does not have a perpendicular termination trench disposed at the first surface of the semiconductor layer.

18. The semiconductor device of Claim 17, wherein the device does not have a p-doped region disposed at an end of the Schottky barrier metal.

19. The semiconductor device of Claim 17, wherein a p-doped region is disposed between the ends of the parallel trenches at an end edge of the Schottky barrier metal, said p-doped region being spaced from the ends of the parallel trenches.

1/19

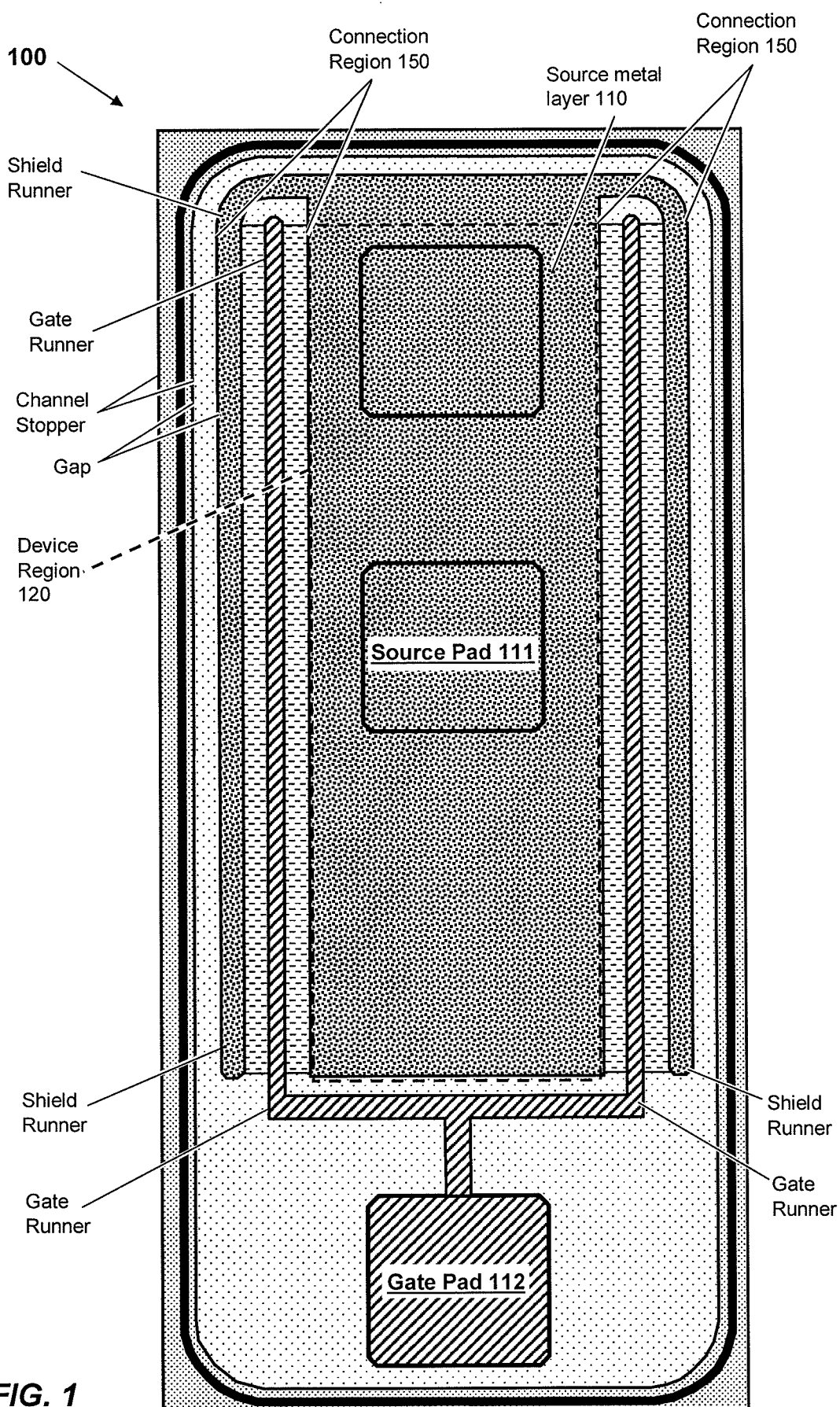


FIG. 1

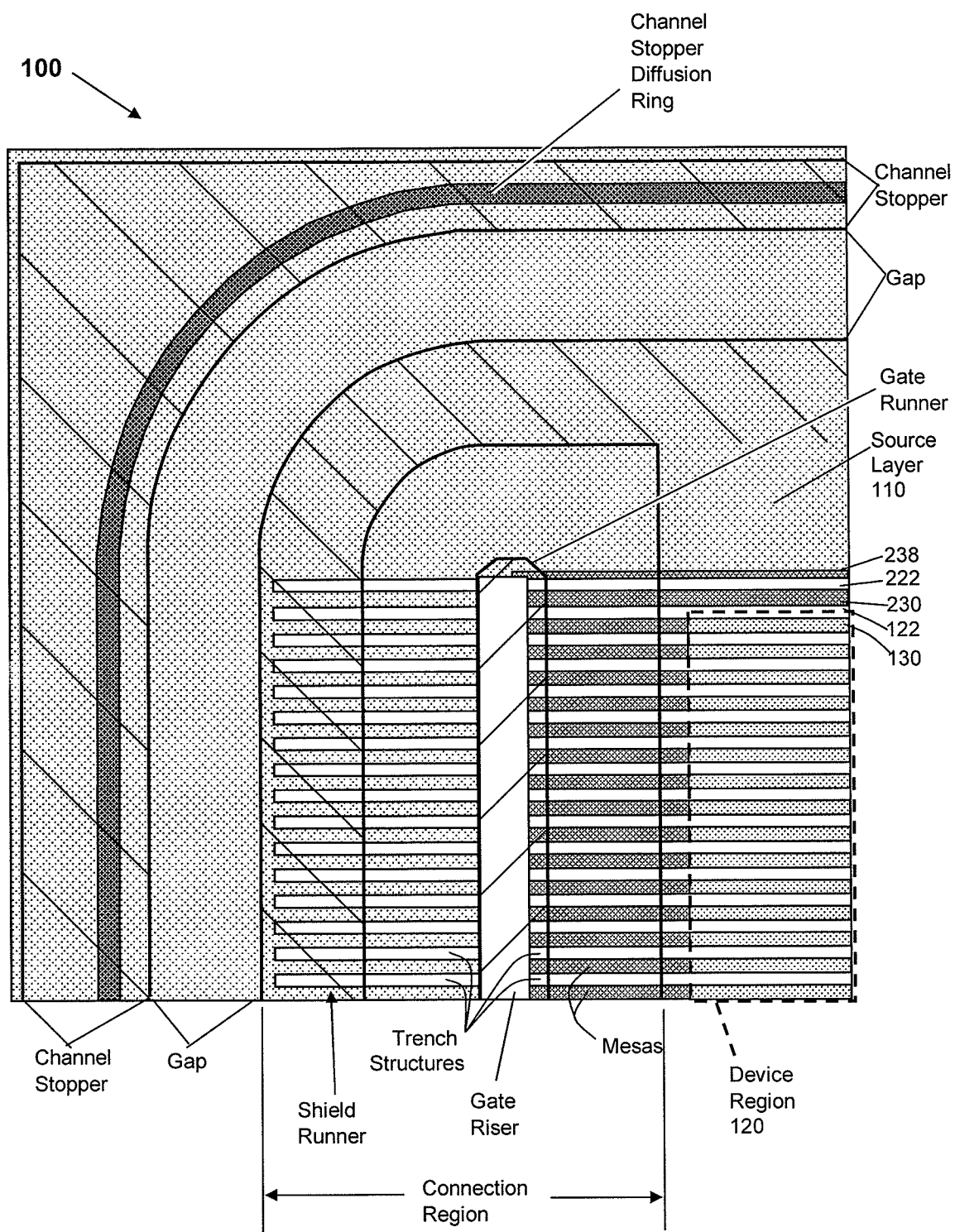


FIG. 2

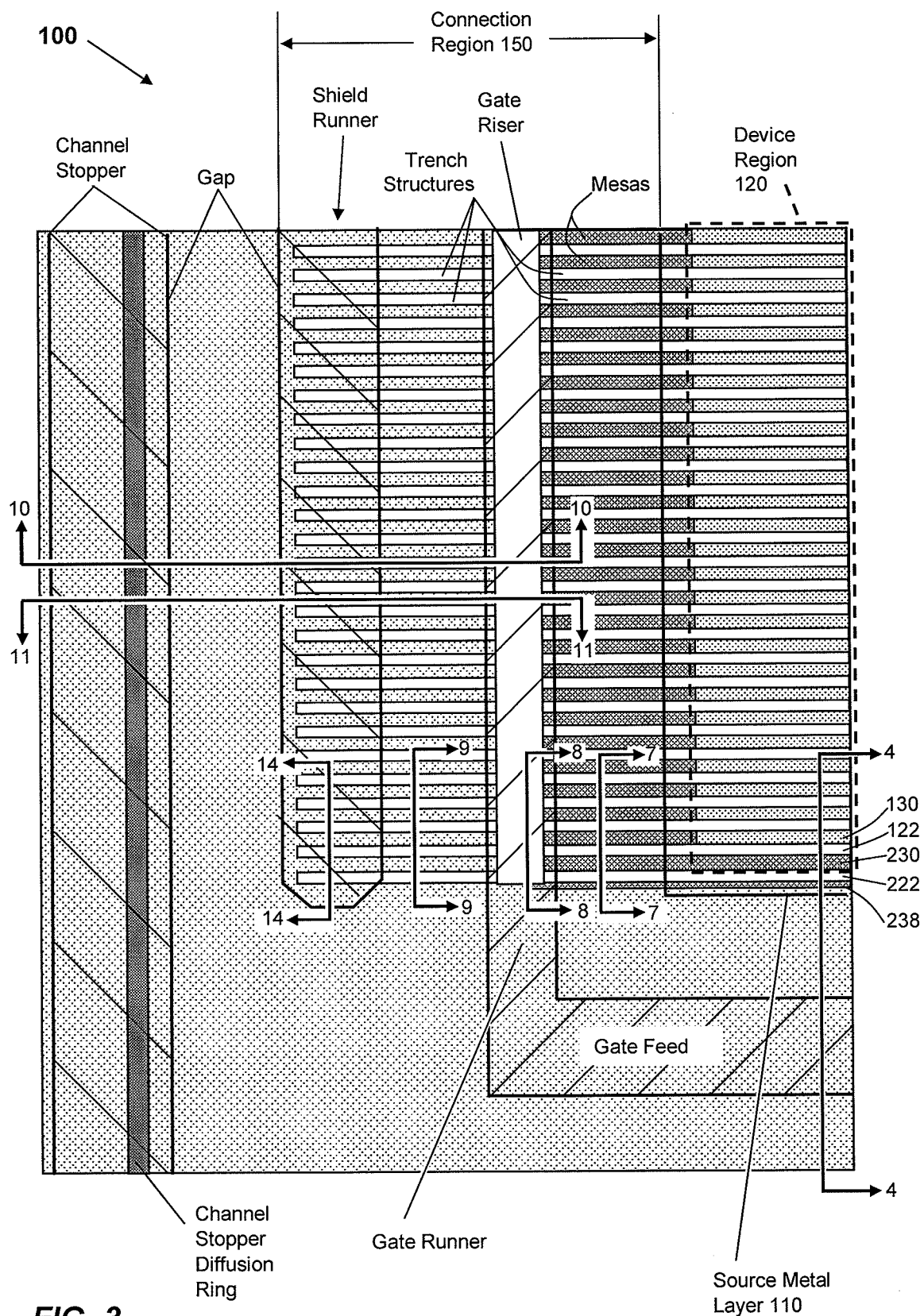


FIG. 3

4/19

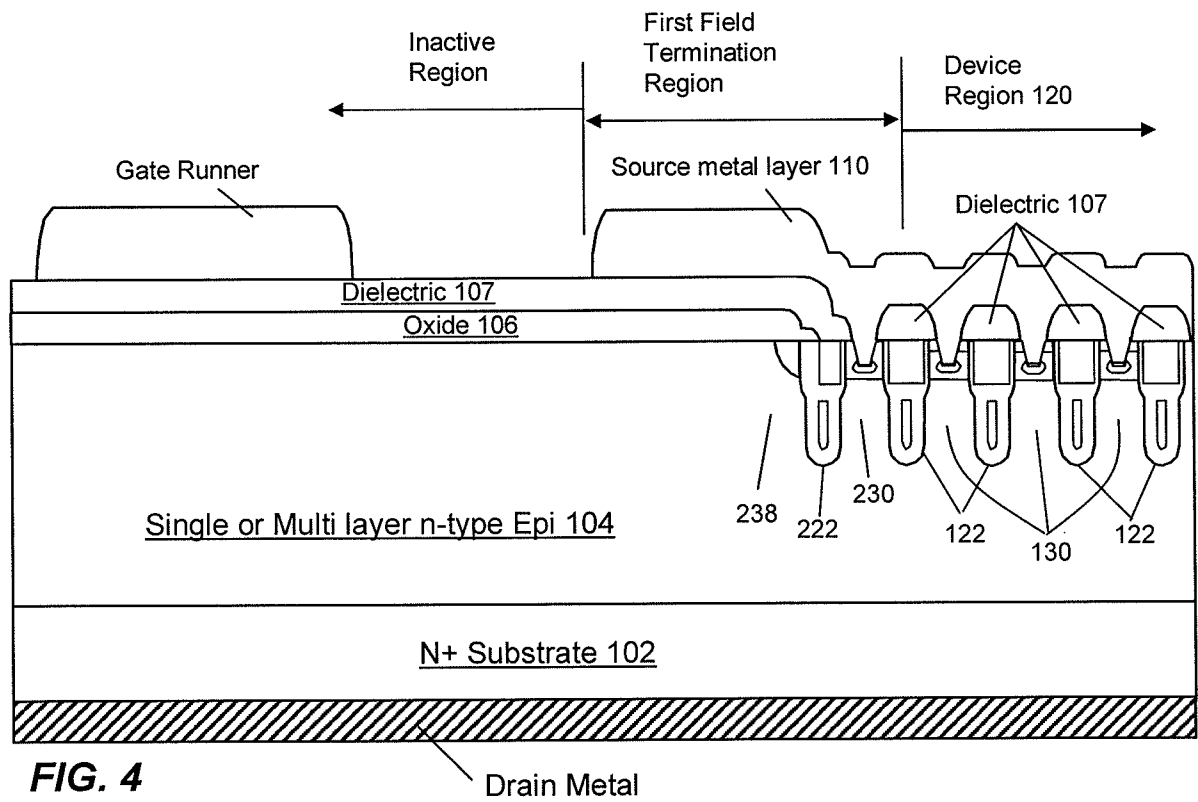


FIG. 4

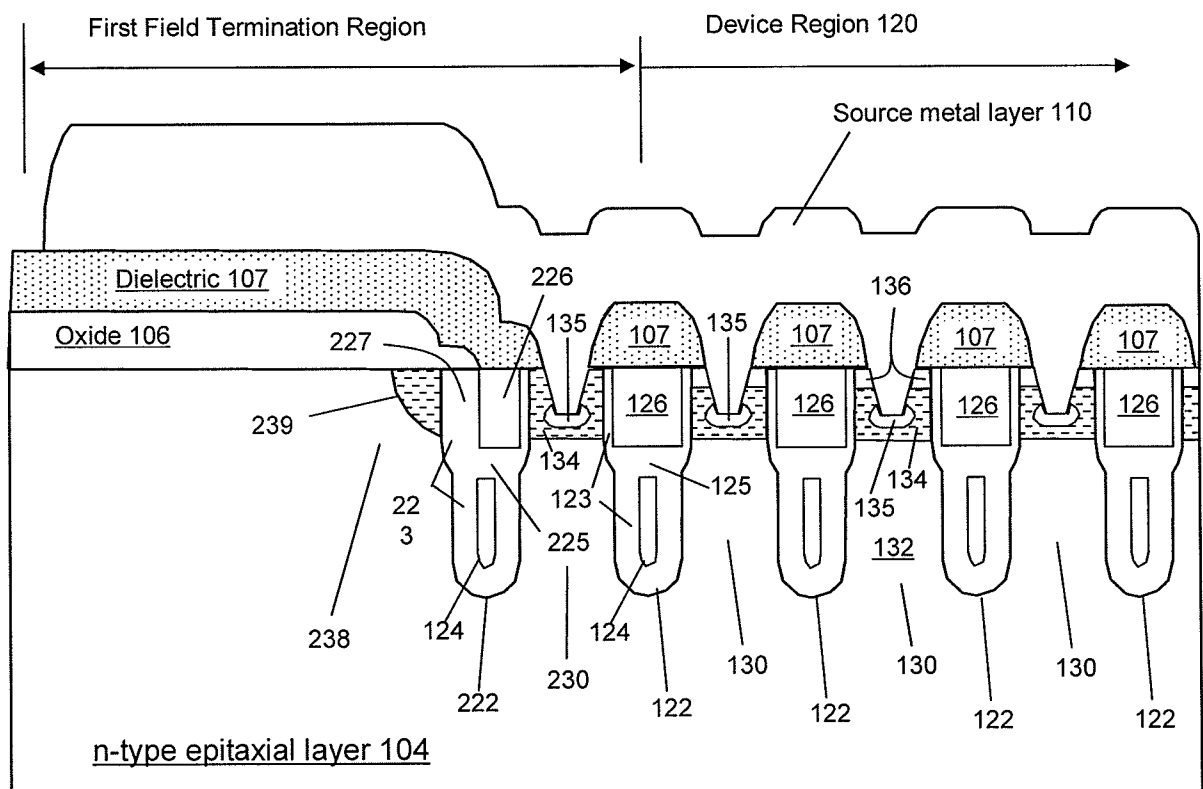


FIG. 5

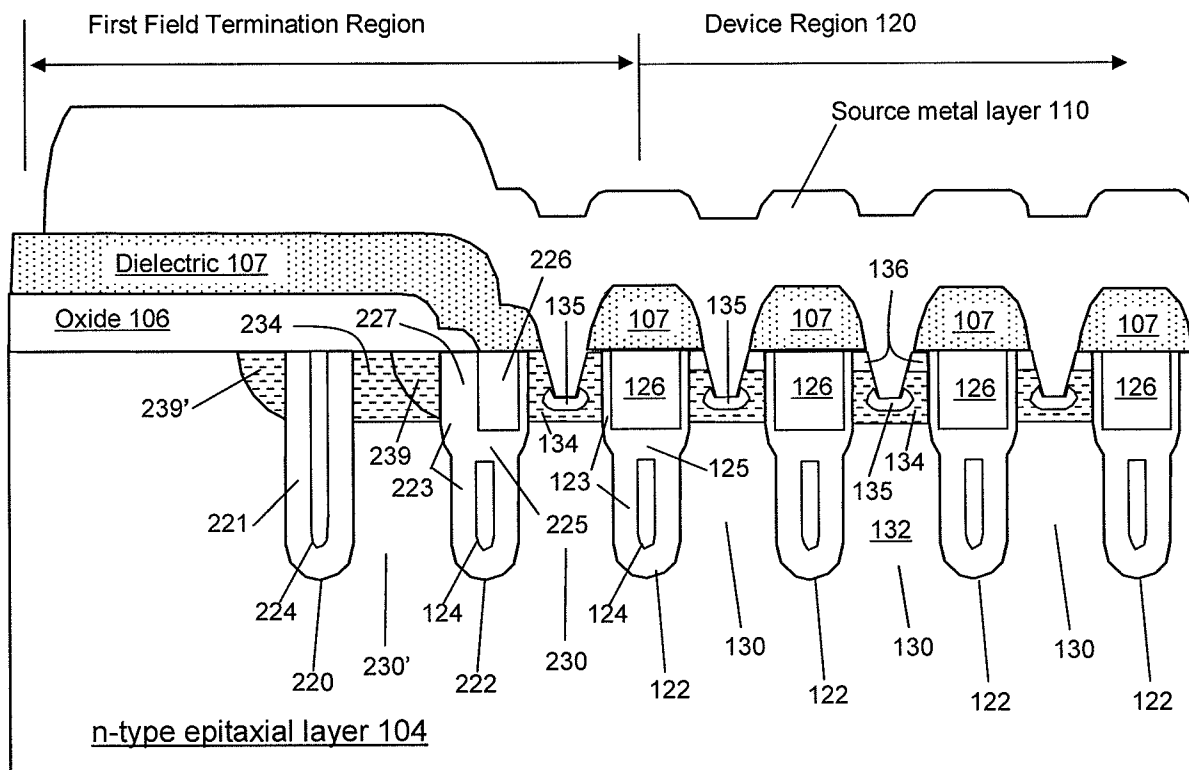


FIG. 6

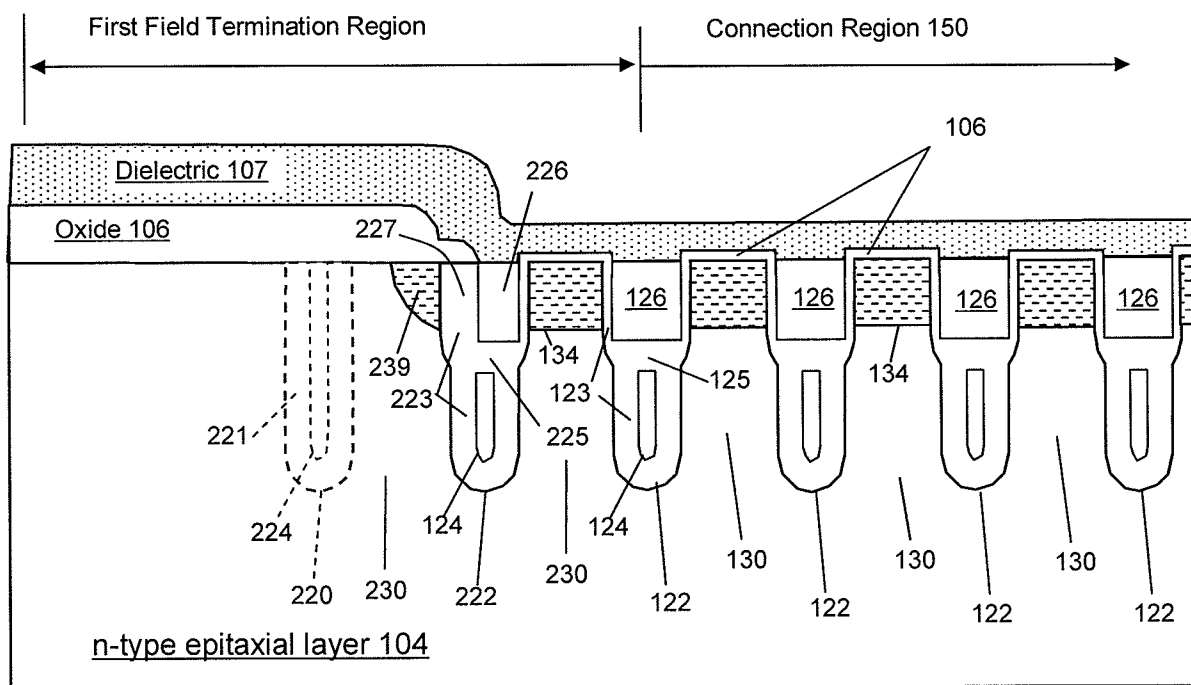


FIG. 7

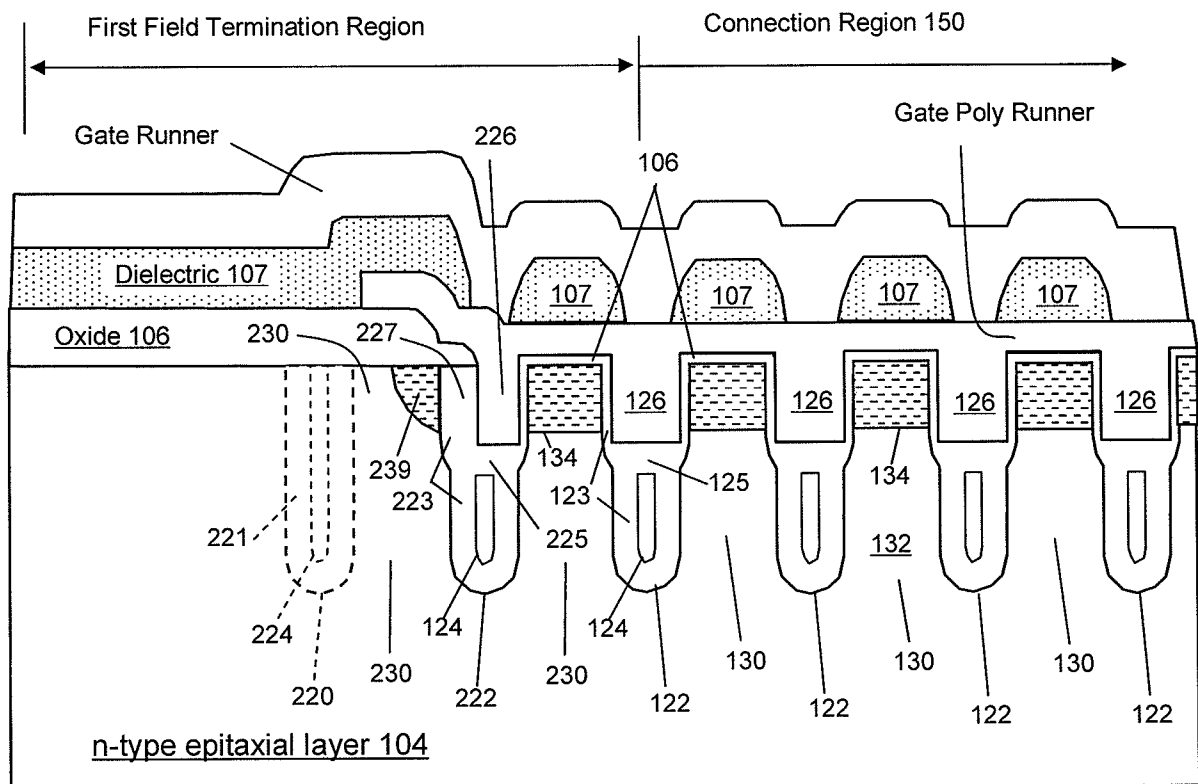


FIG. 8

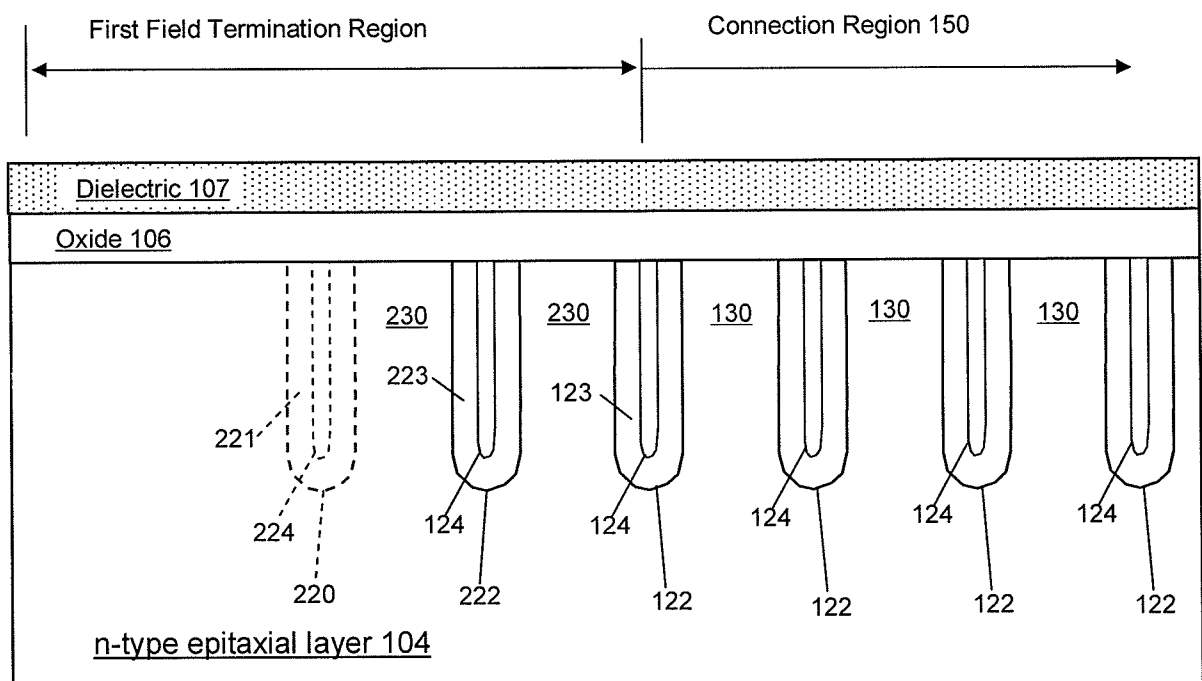


FIG. 9

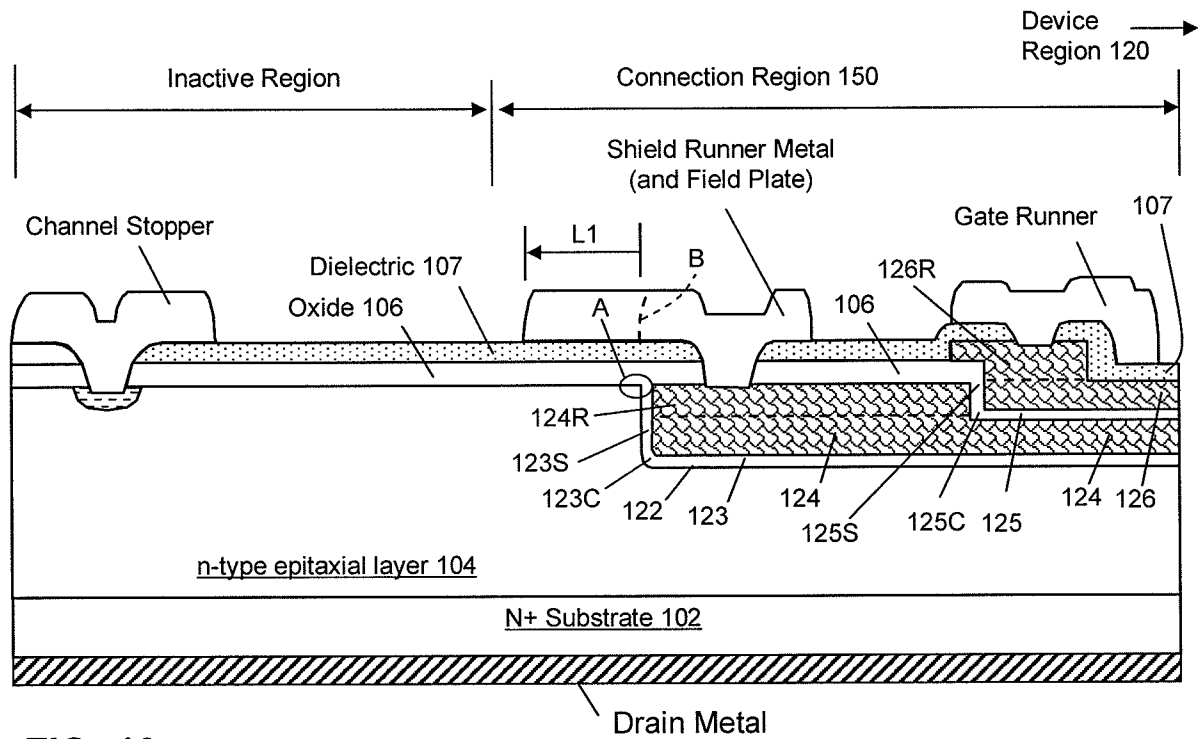


FIG. 10

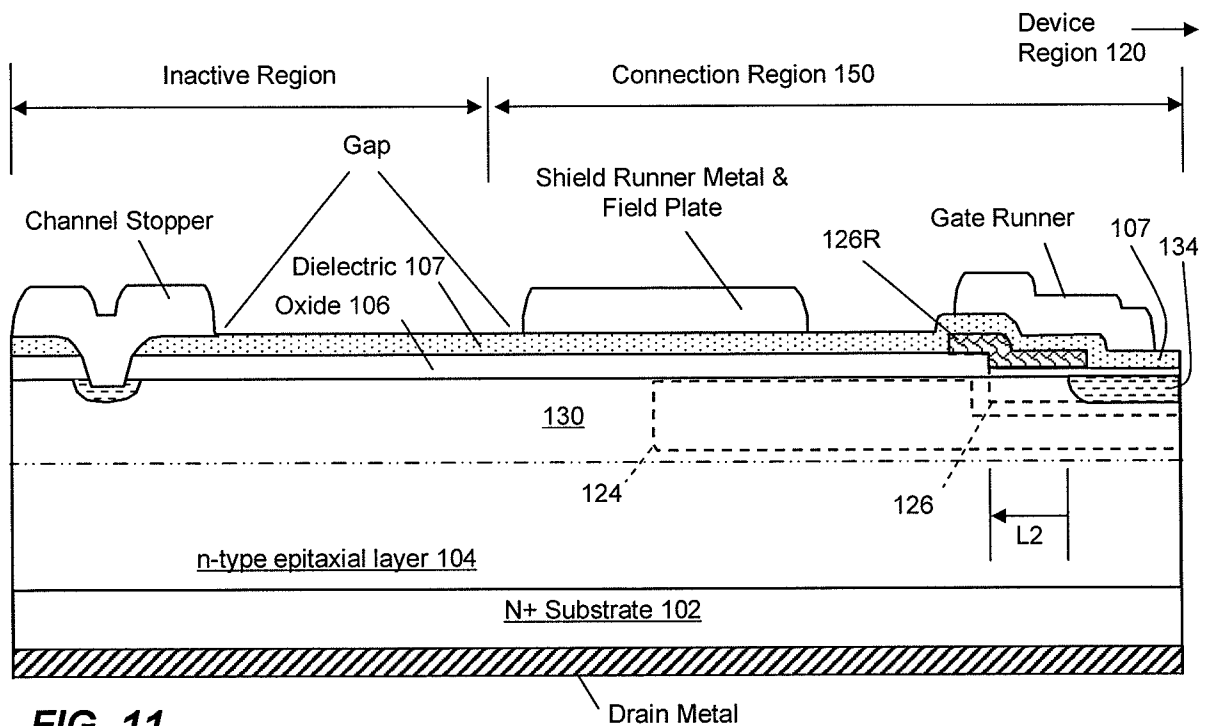


FIG. 11

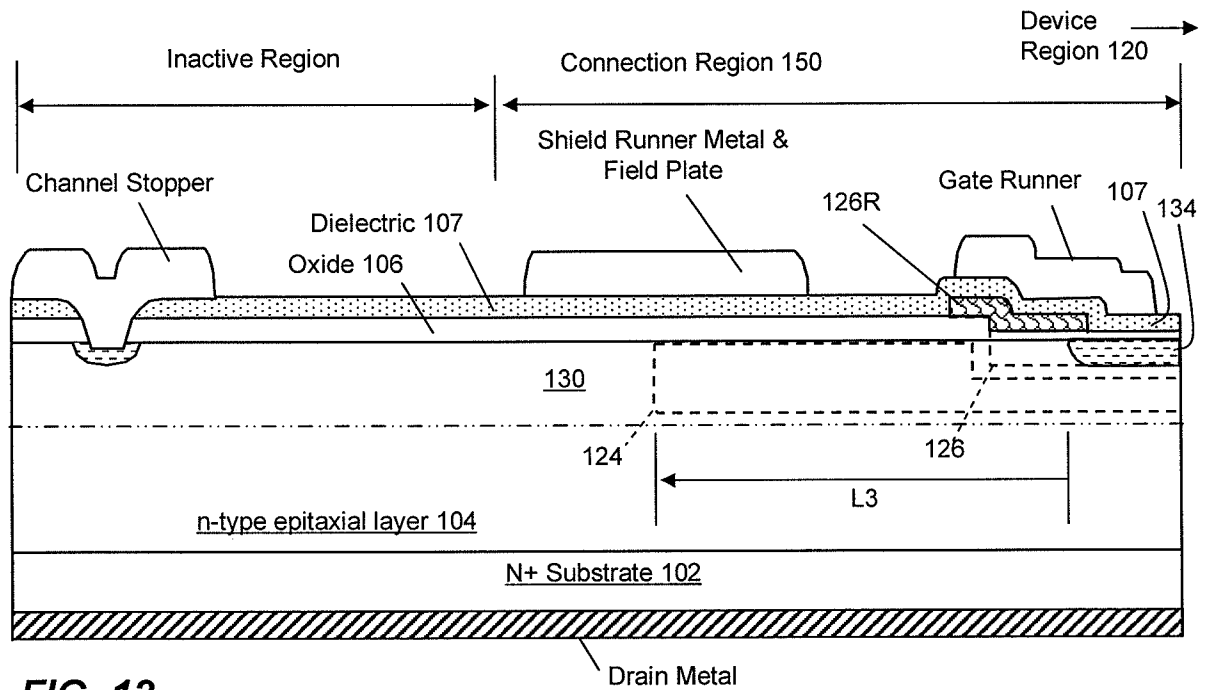


FIG. 12

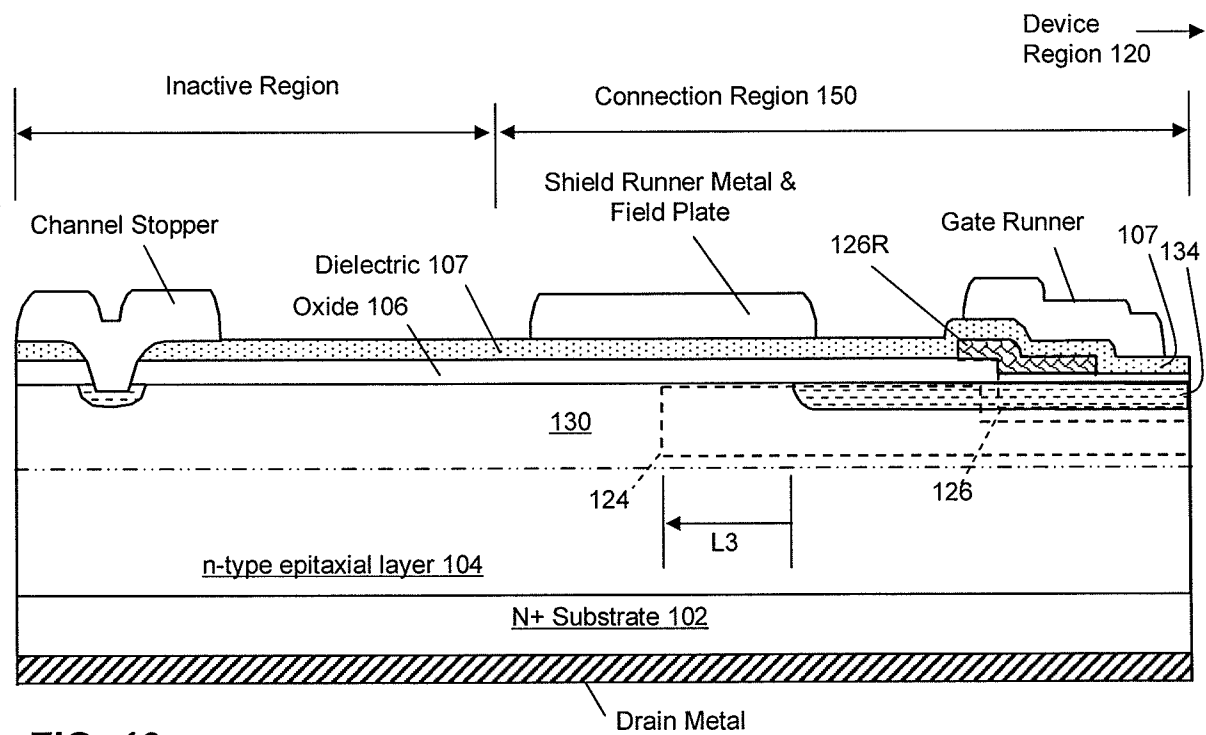
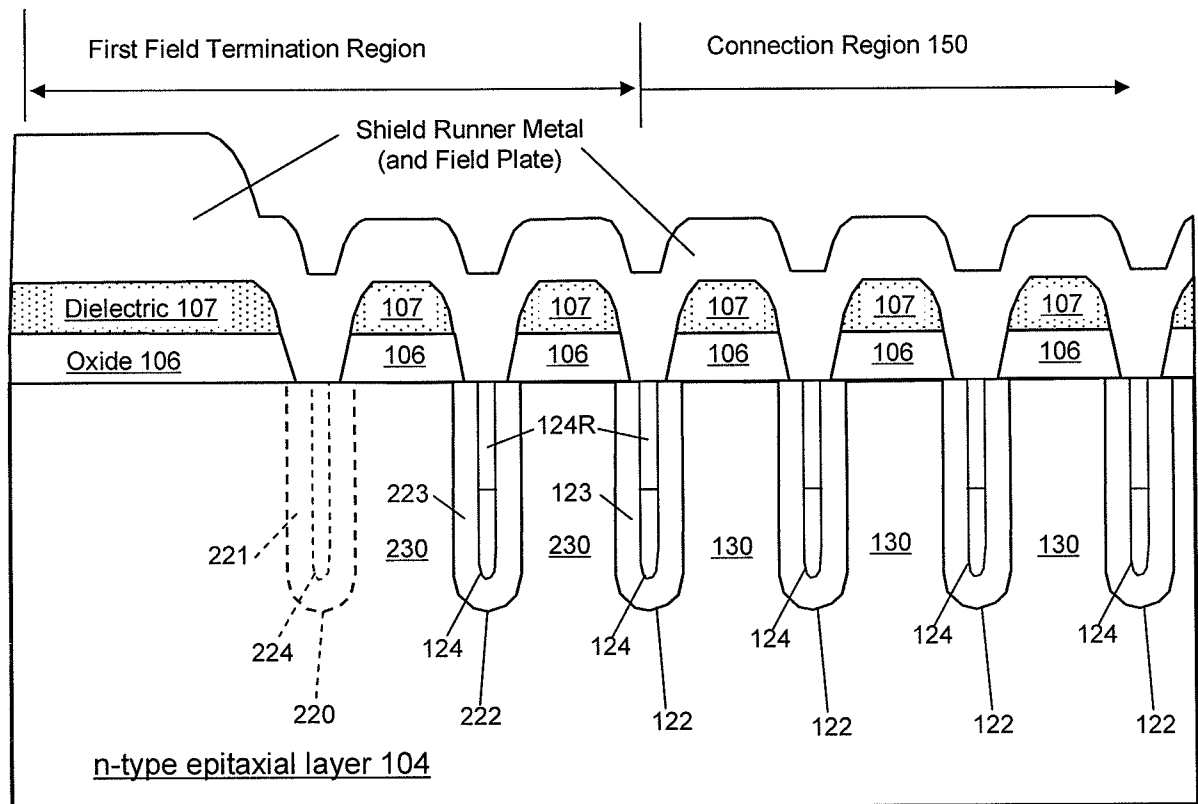
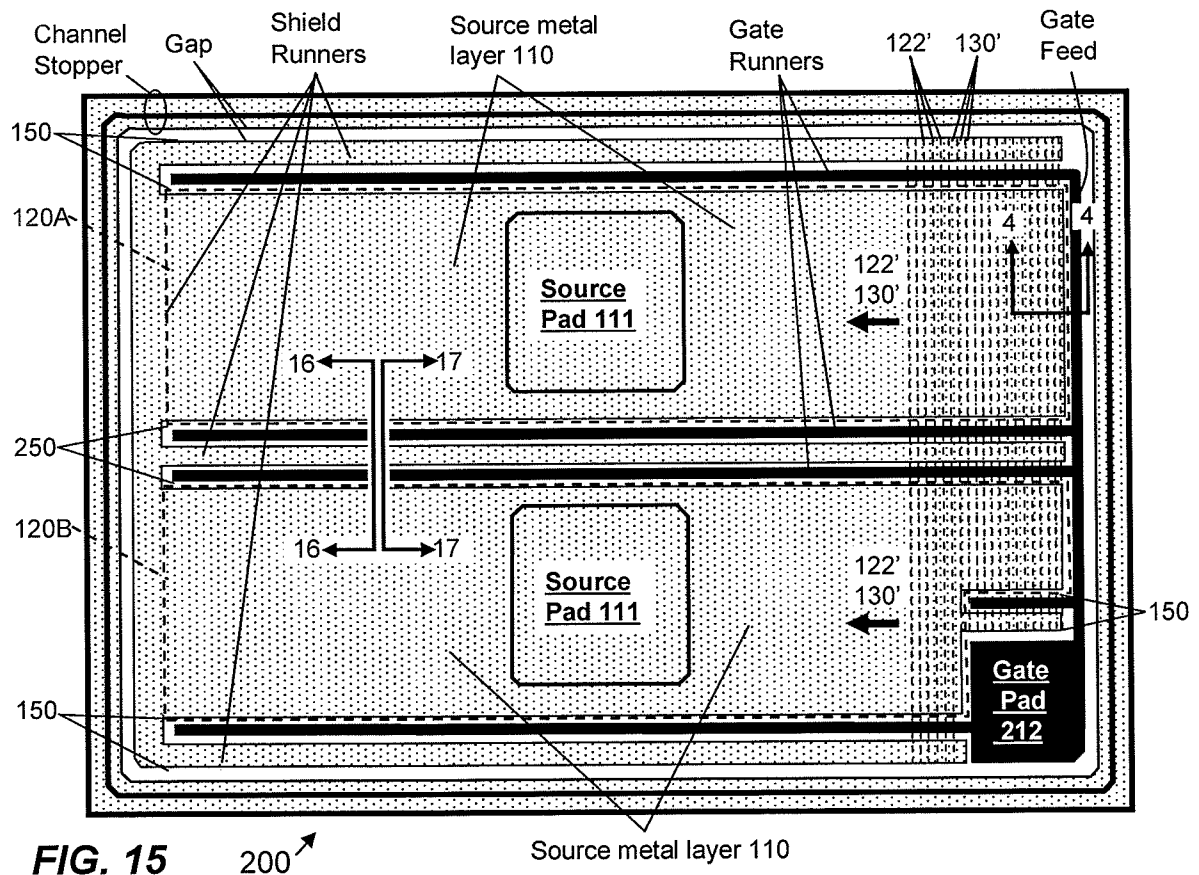
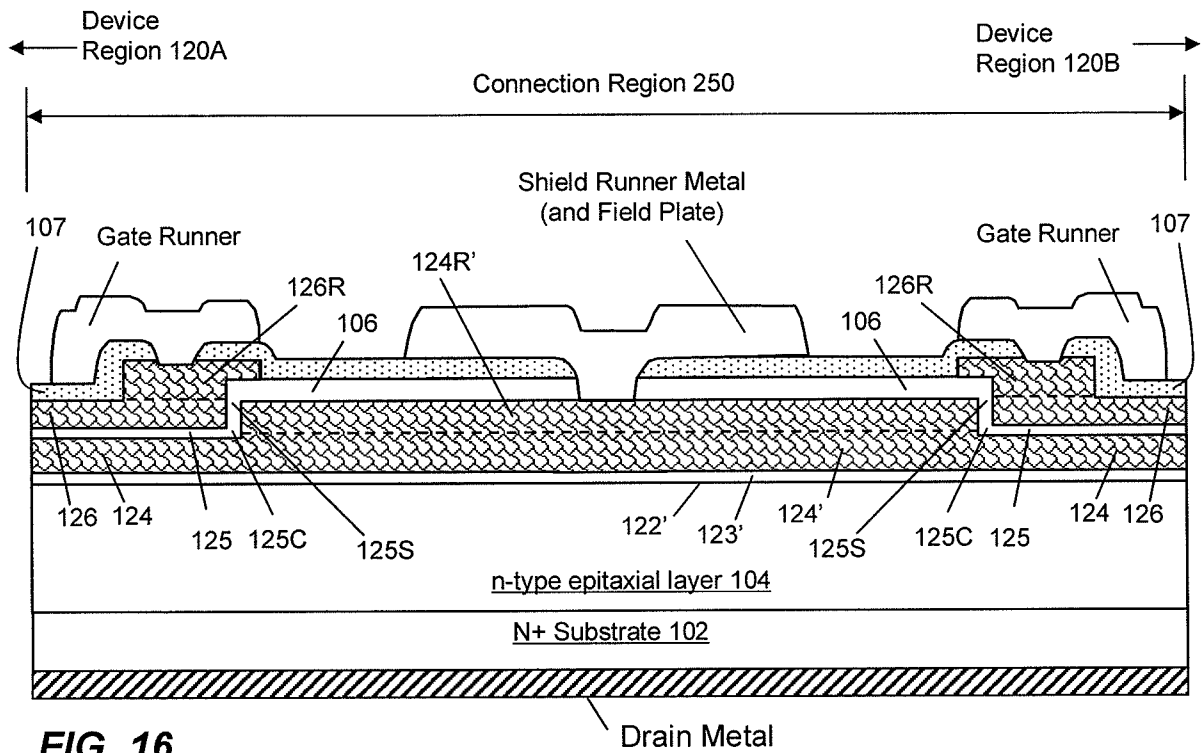
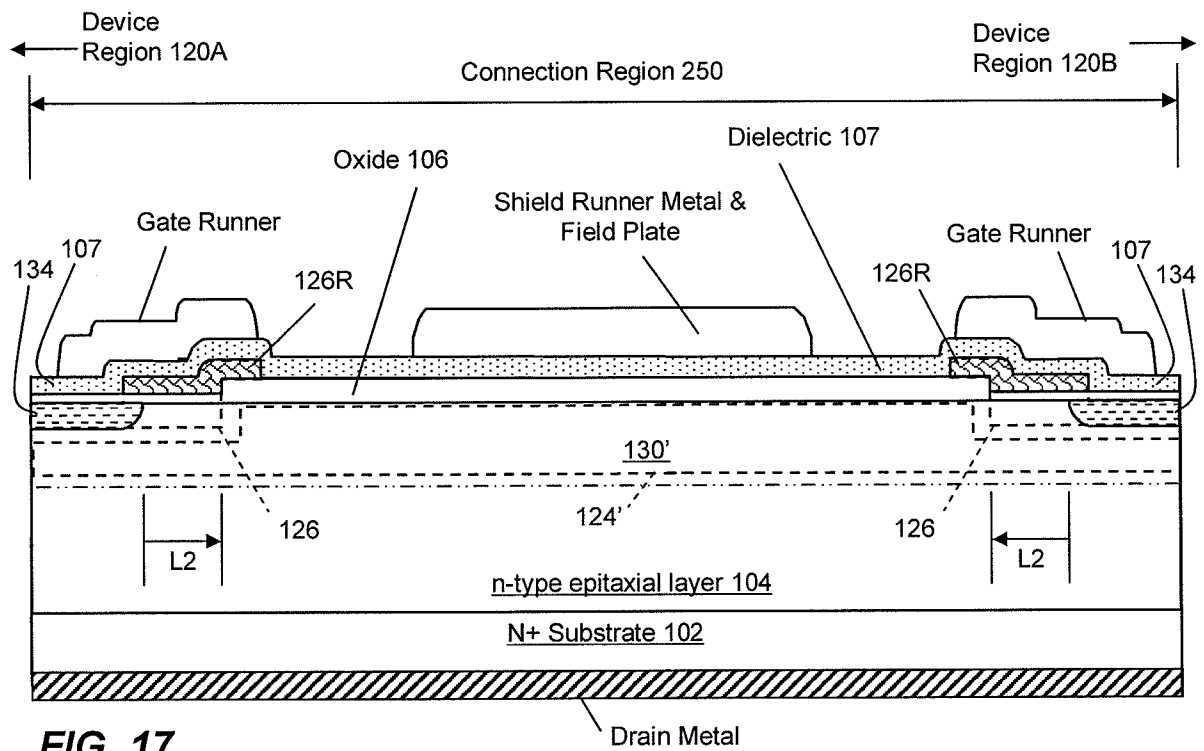


FIG. 13

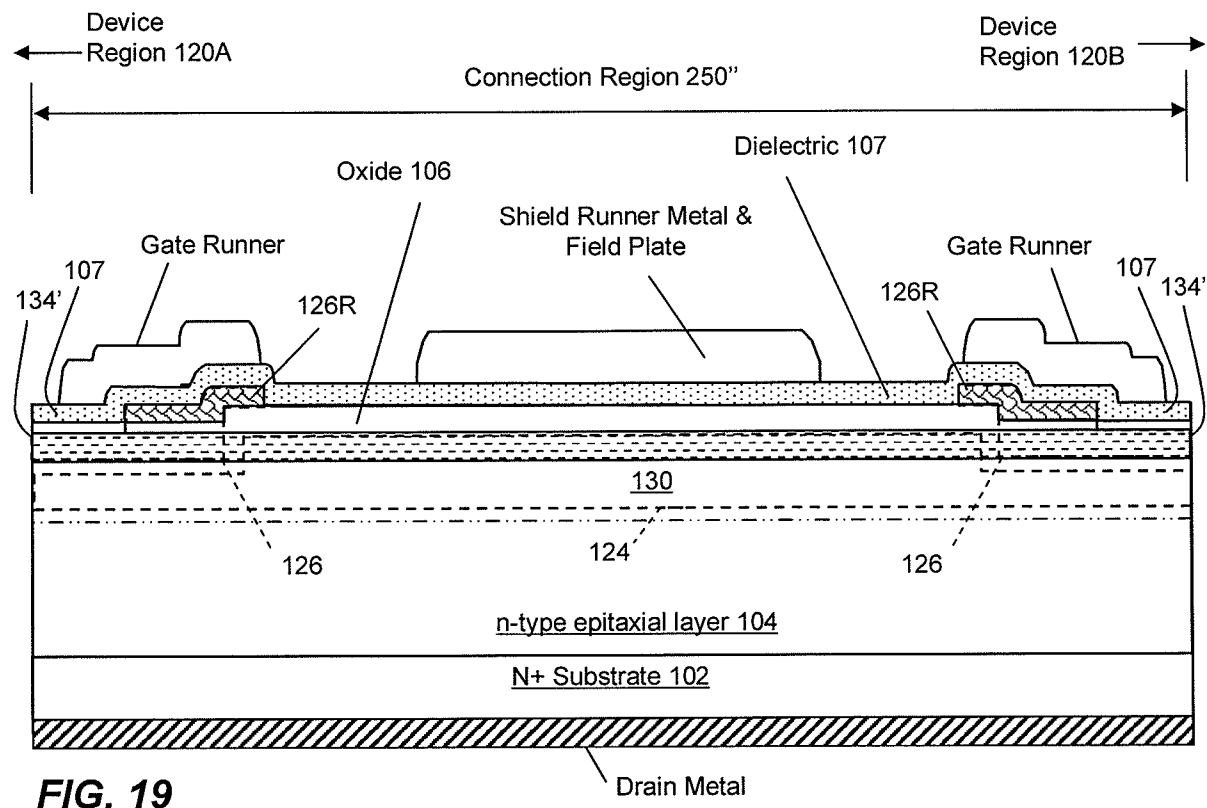
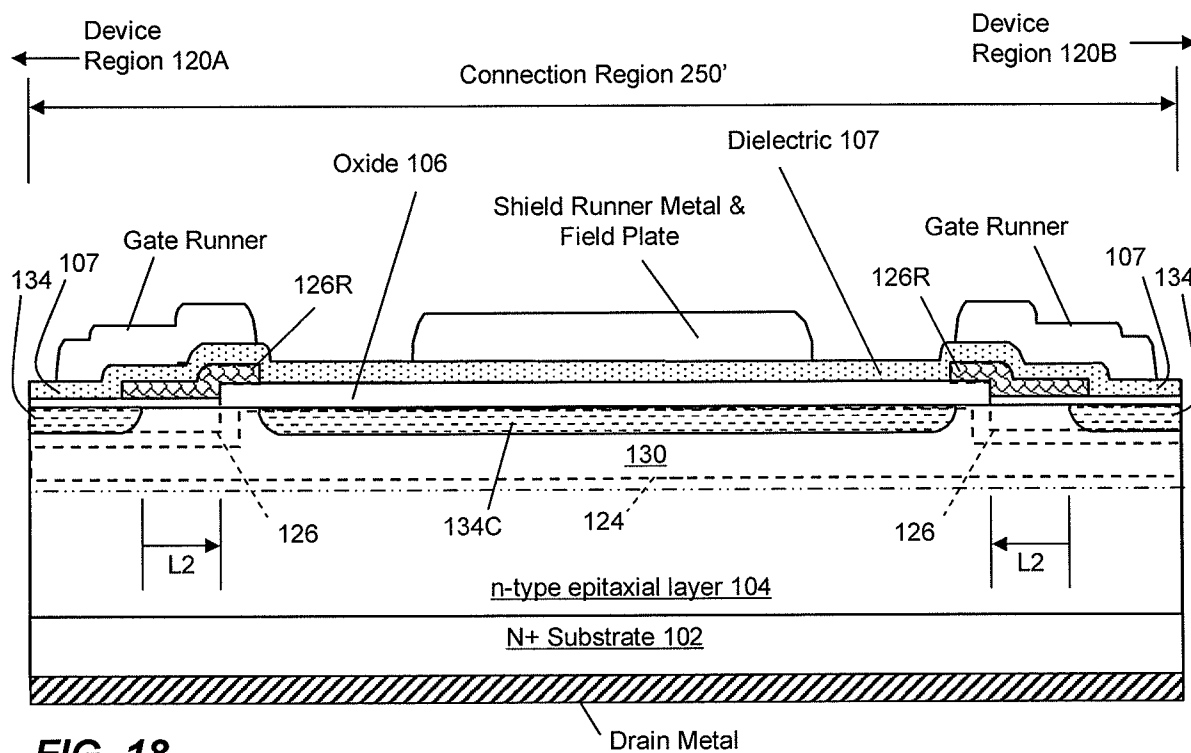
9/19

**FIG. 14****FIG. 15**

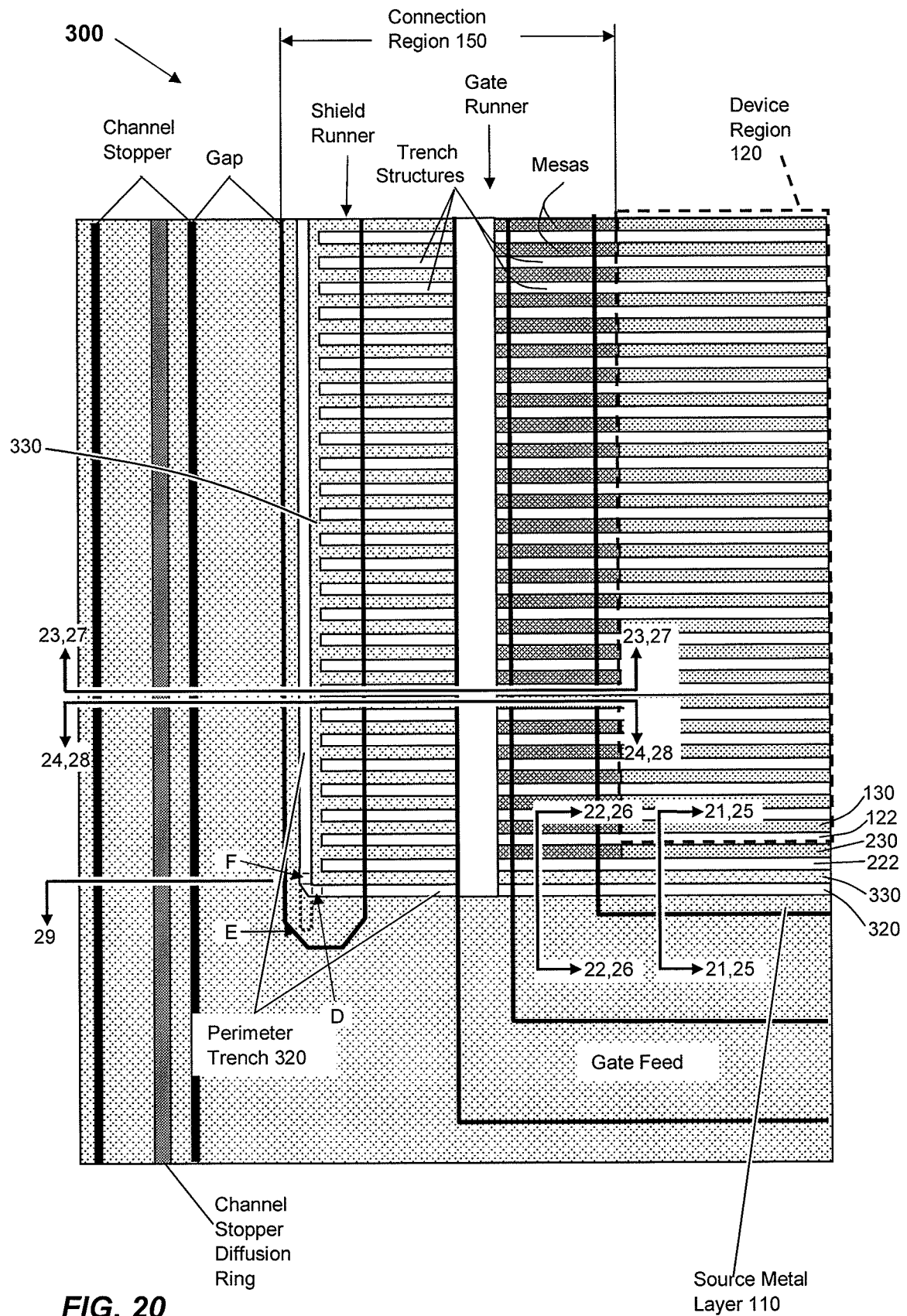
10/19

**FIG. 16****FIG. 17**

11/19



12/19

**FIG. 20**

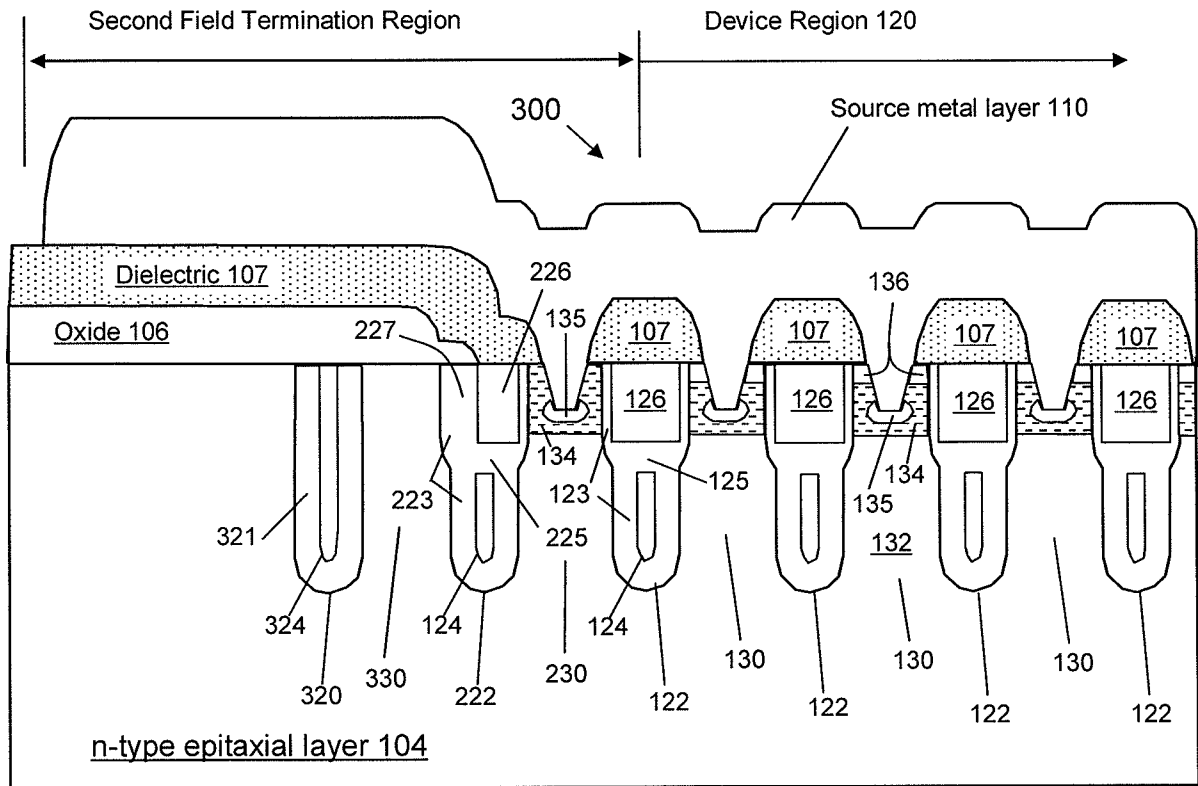


FIG. 21

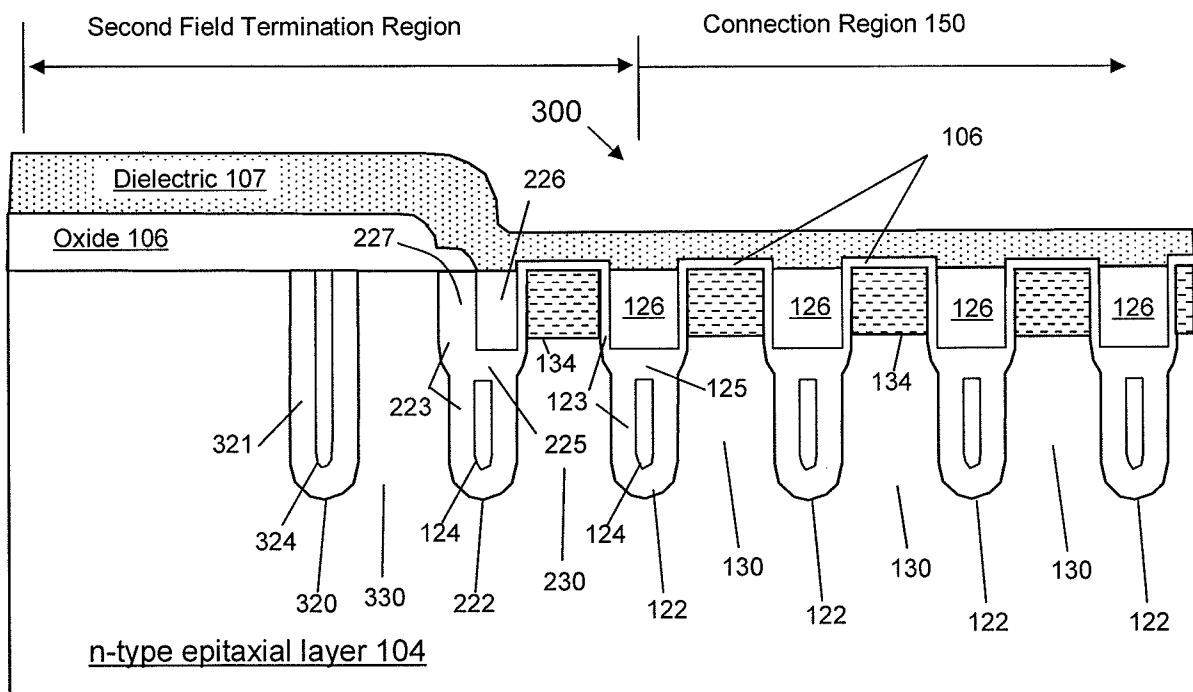


FIG. 22

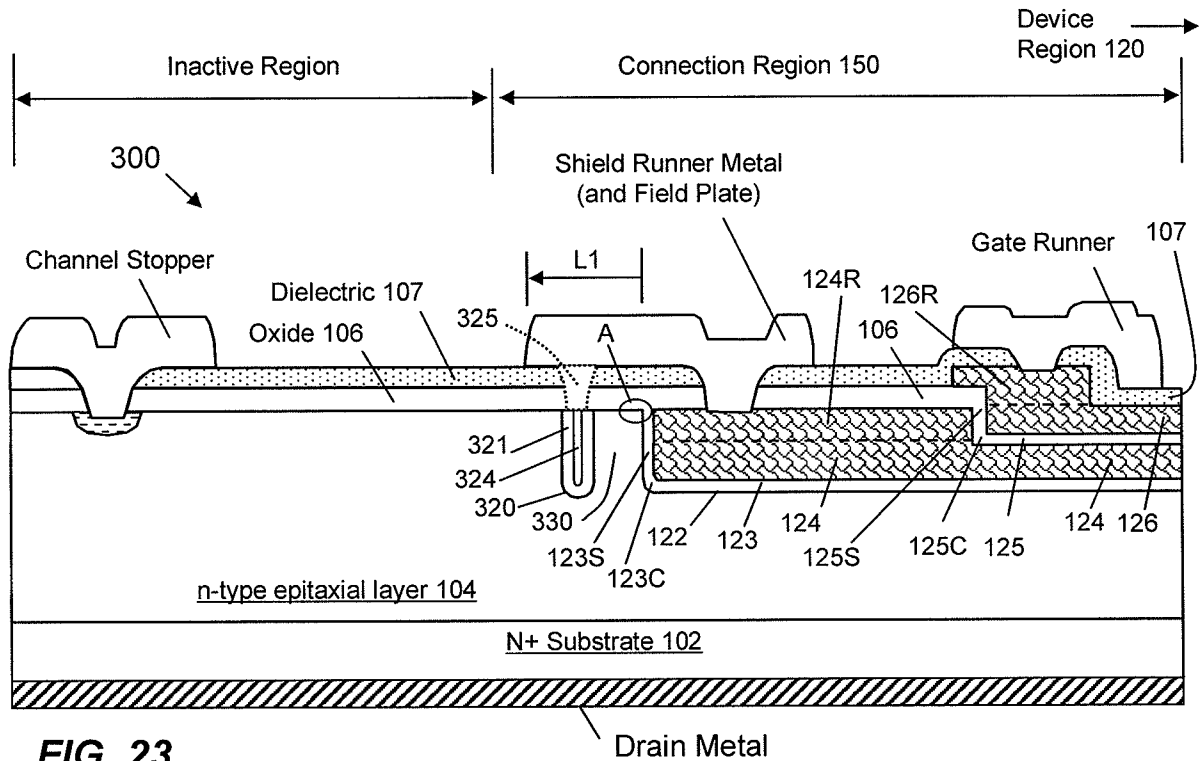


FIG. 23

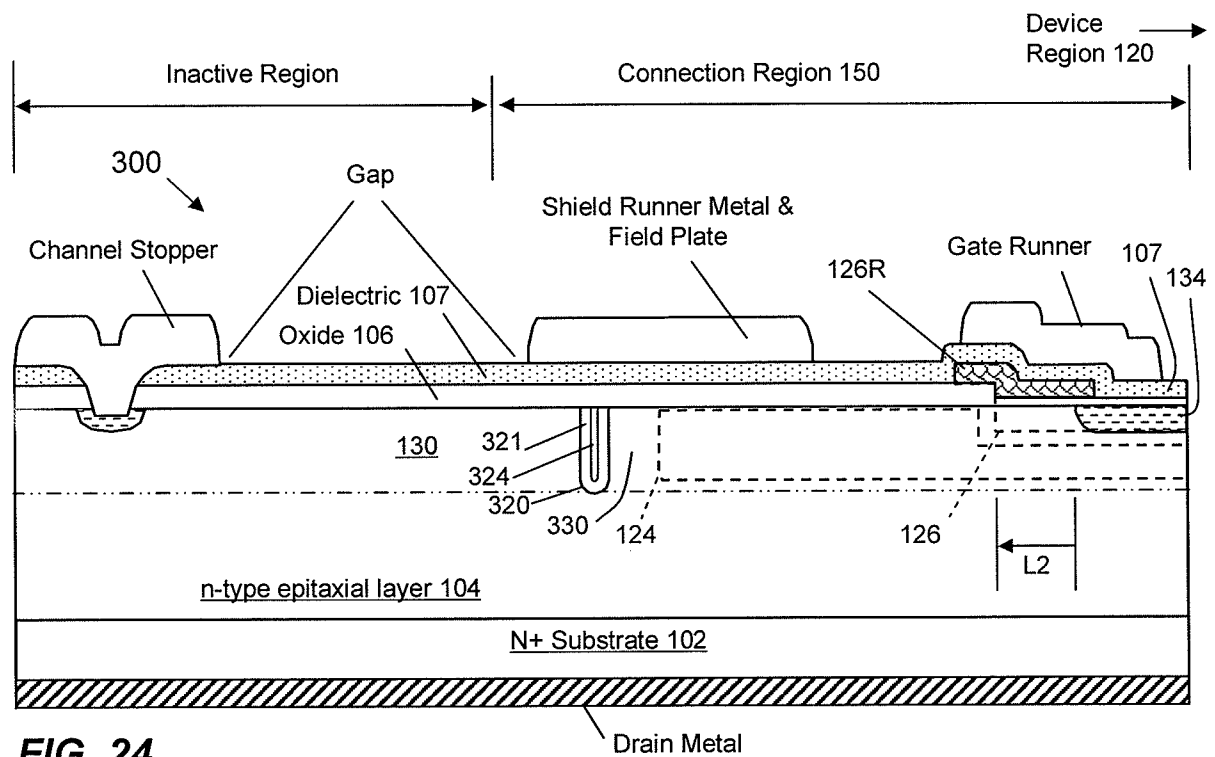


FIG. 24

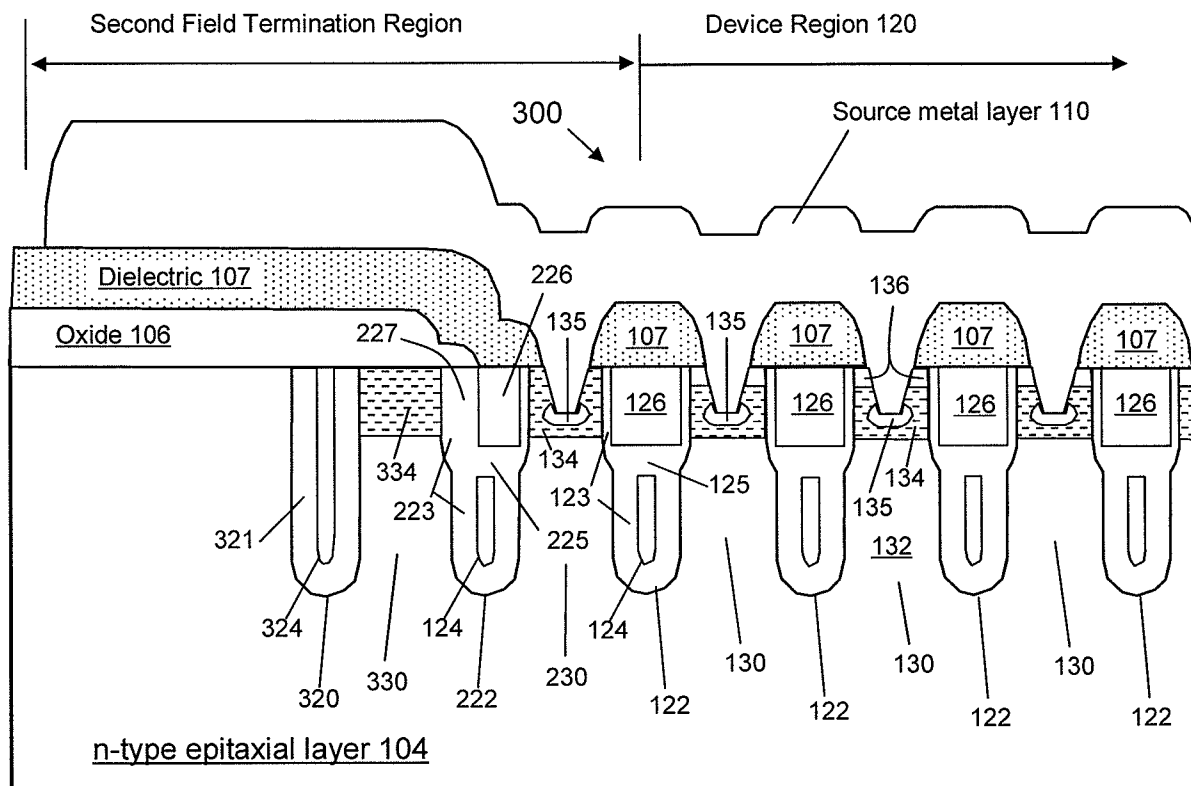


FIG. 25

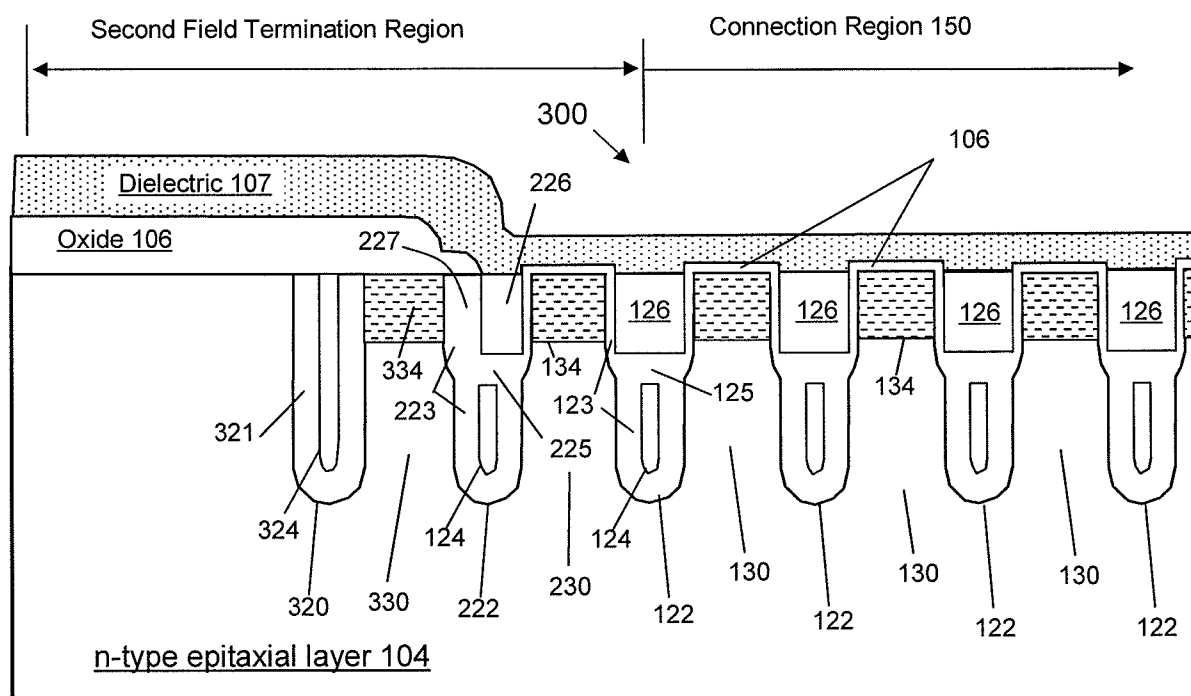


FIG. 26

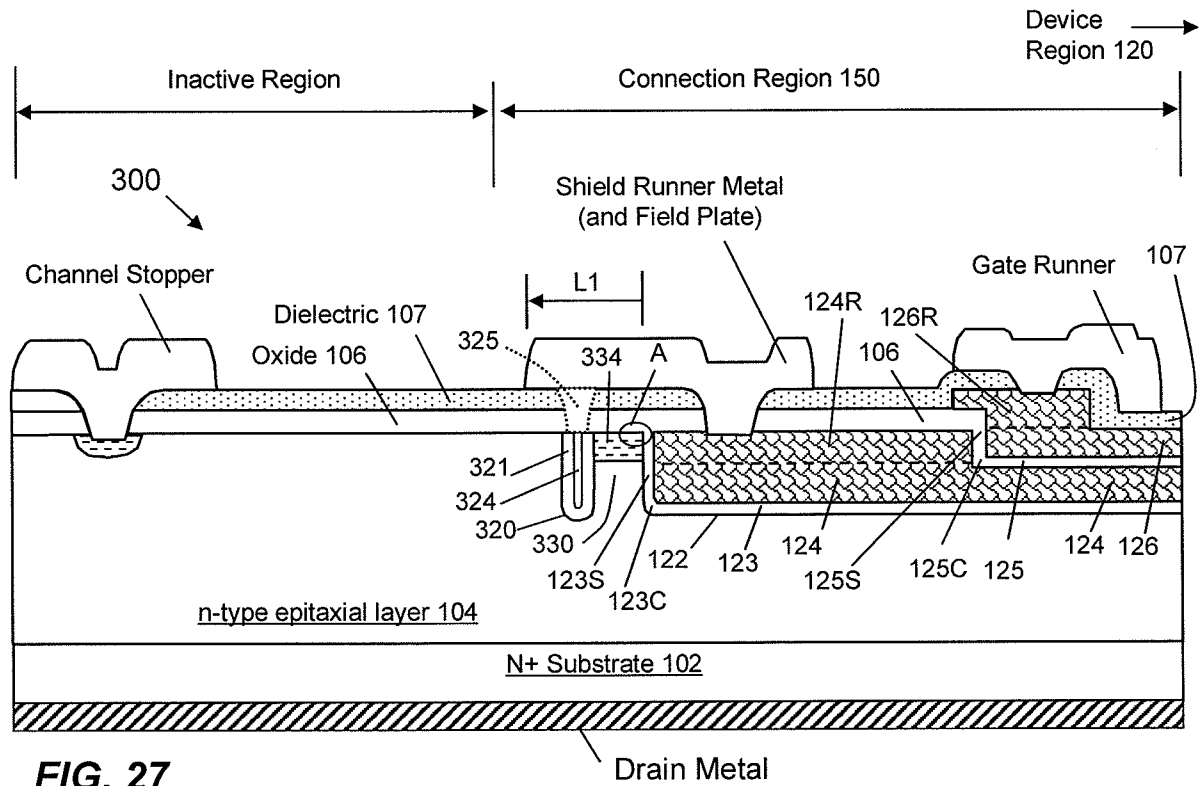


FIG. 27

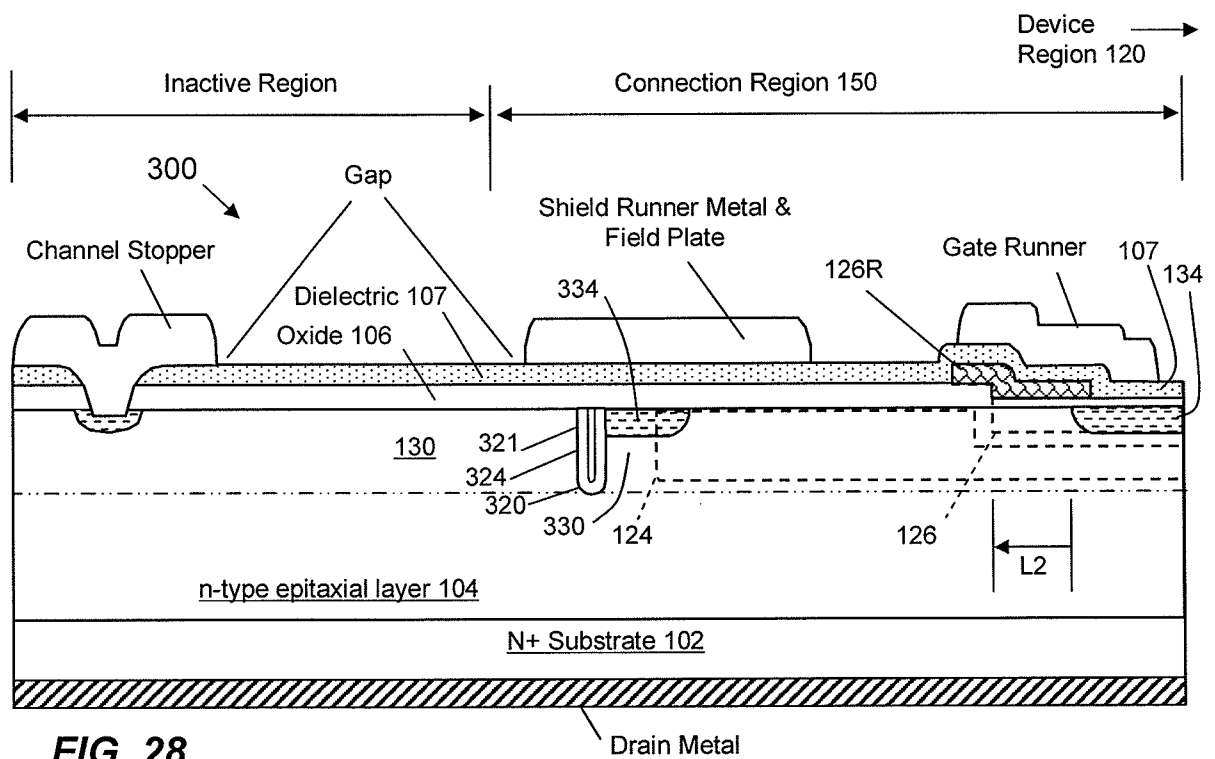


FIG. 28

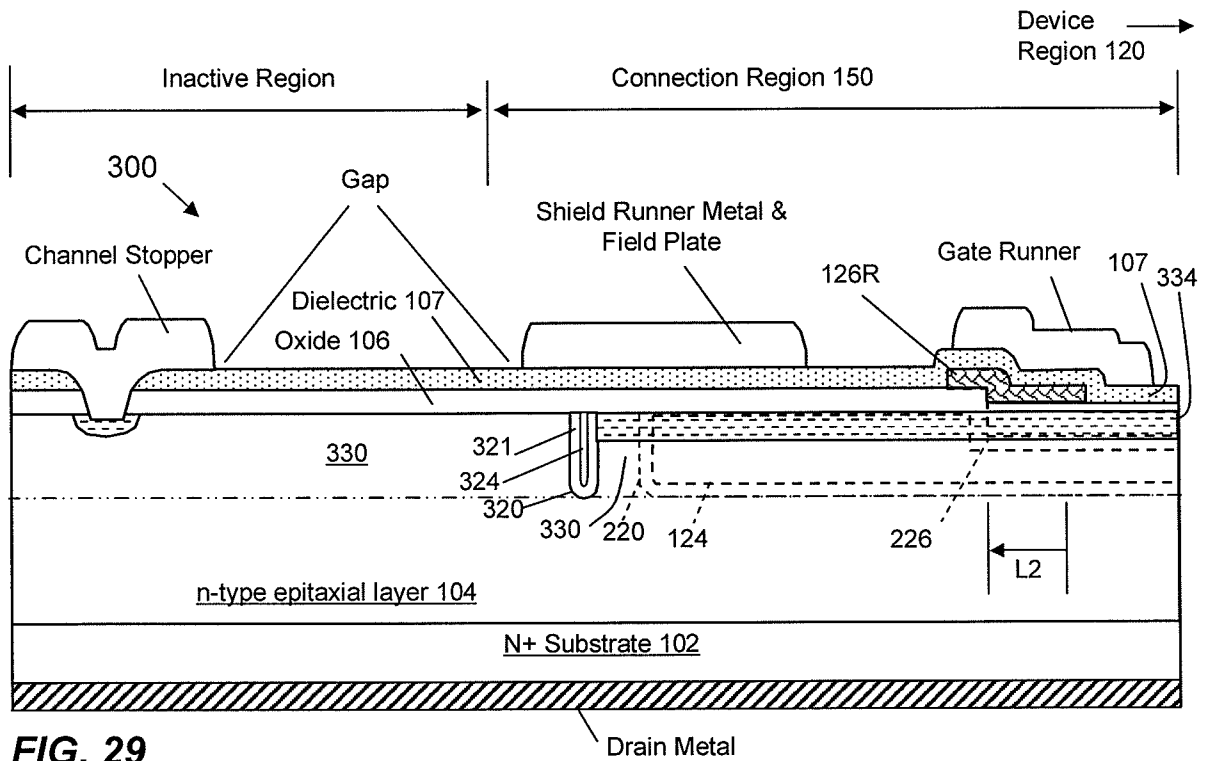
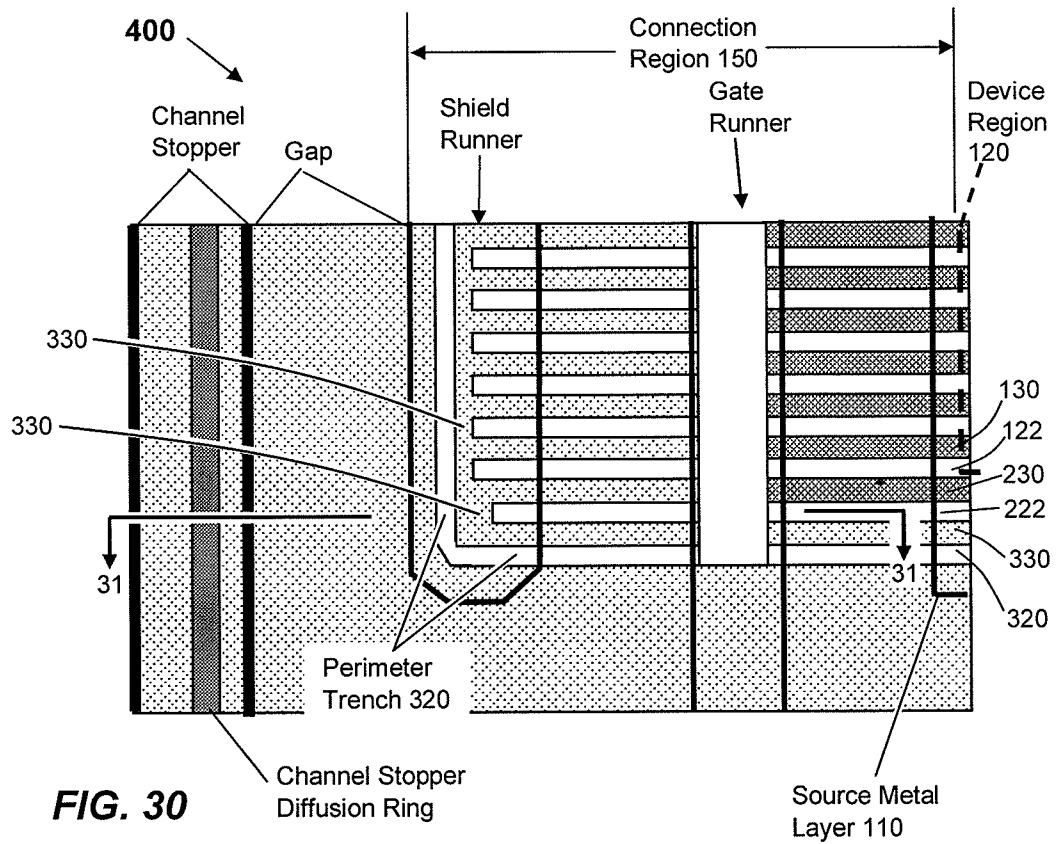
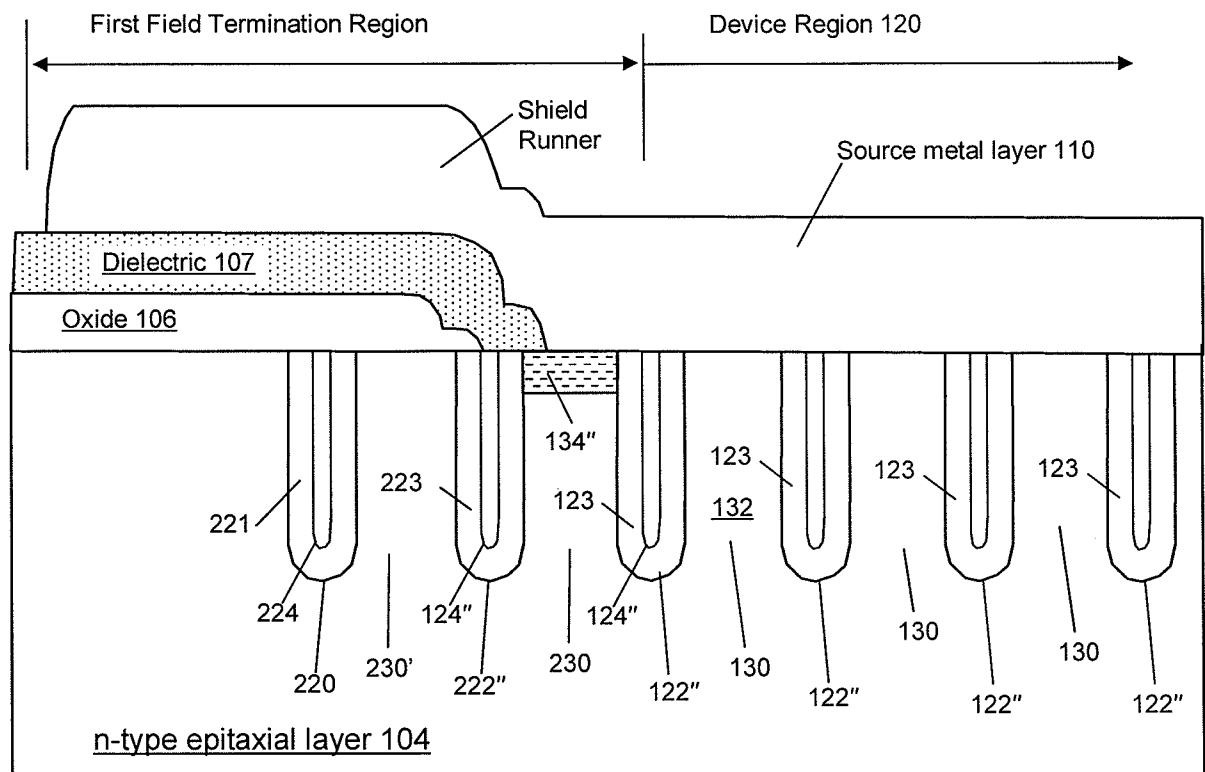
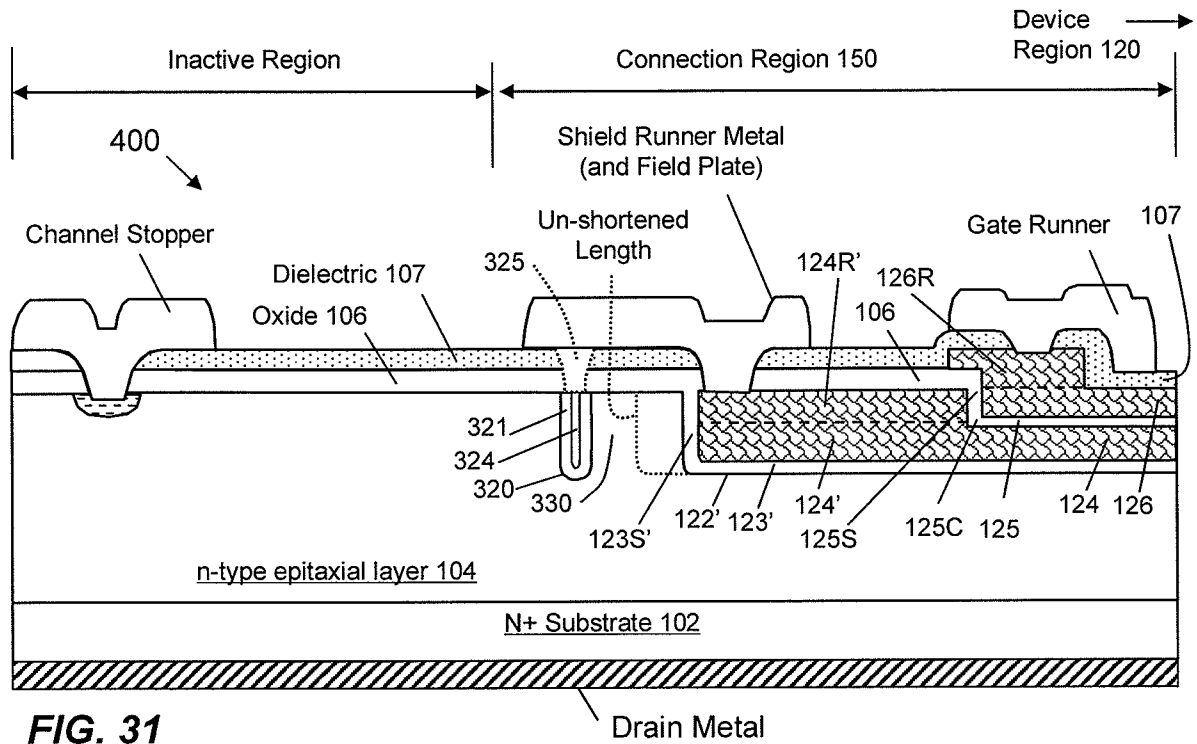


FIG. 29





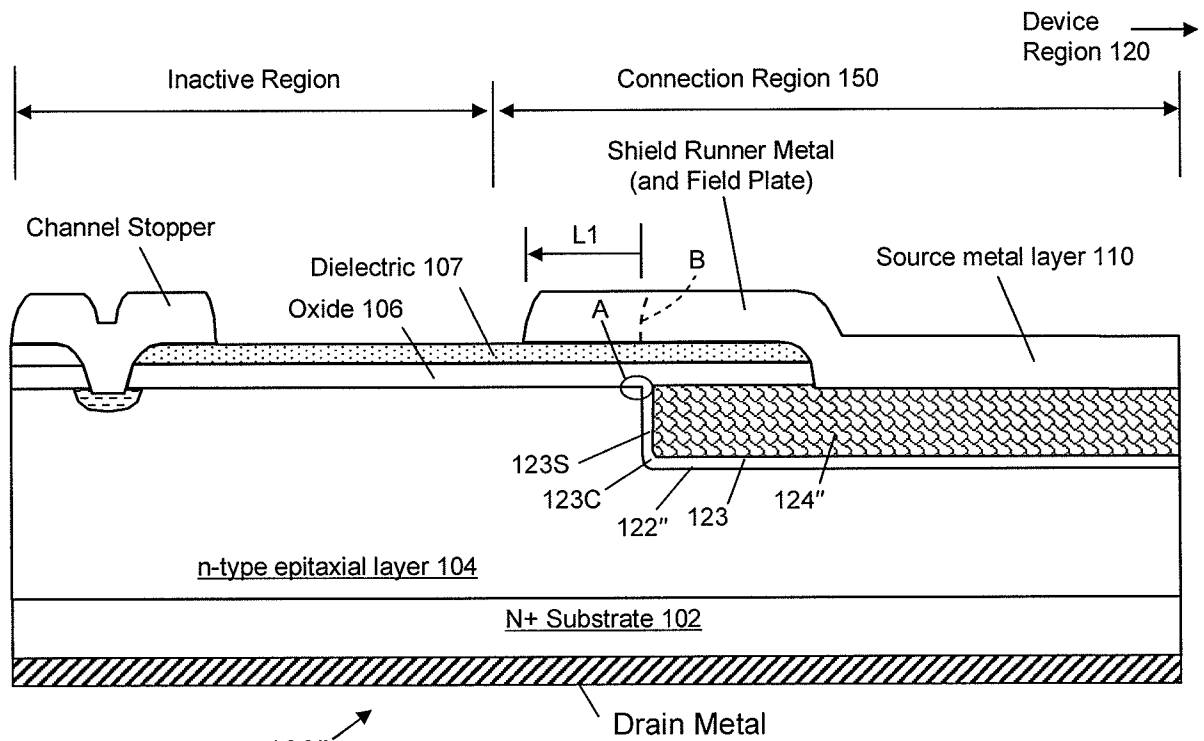


FIG. 33

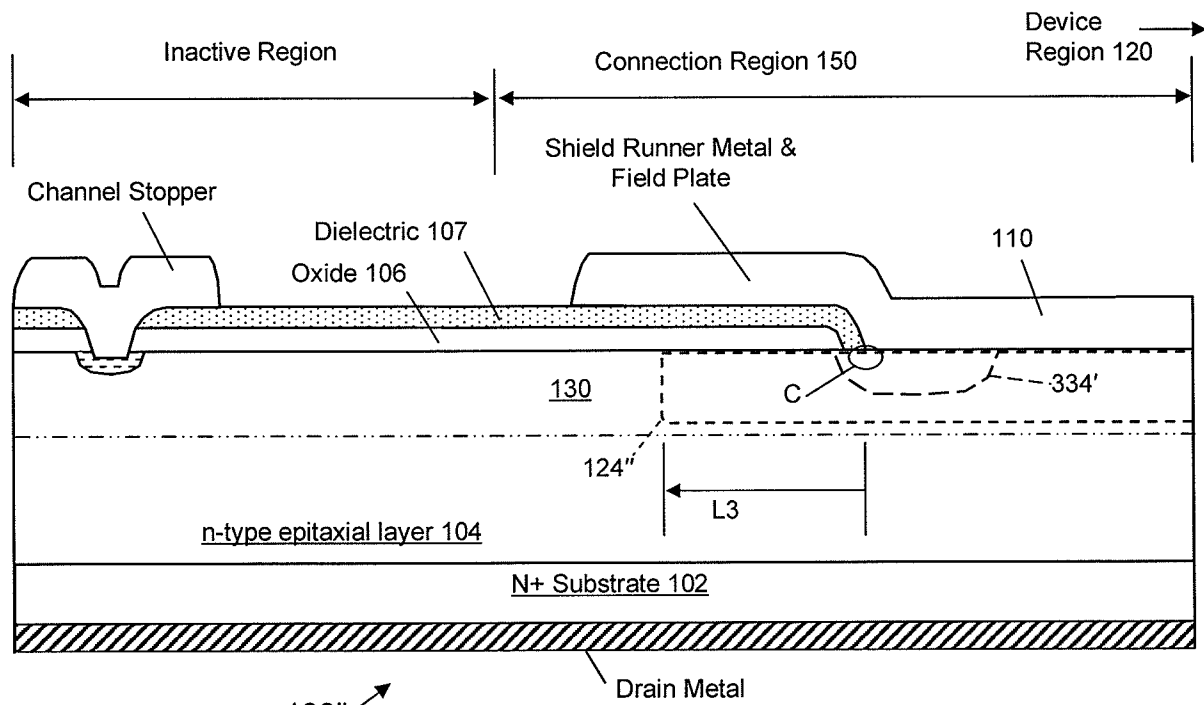


FIG. 34

A. CLASSIFICATION OF SUBJECT MATTER**H01L 29/78(2006.01)i, H01L 21/336(2006.01)i**

According to International Patent Classification (IPC) or to both national classification and IPC

B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols)

H01L 29/78; H01L 21/3205; H01L 21/336; H01L 21/8242; H01L 29/94

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Korean utility models and applications for utility models

Japanese utility models and applications for utility models

Electronic data base consulted during the international search (name of data base and, where practicable, search terms used)

eKOMPASS(KIPO internal) & Keywords:trench, semiconductor, dielectric layer, sidewall

C. DOCUMENTS CONSIDERED TO BE RELEVANT

Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
A	US 2007-0190728 A1 (SREEVATSA SREEKANTHAM et al.) 16 August 2007 See abstract, figures 1-12 and claims 1-18.	1-19
A	WO 2006-127914 A2 (FAIRCHILD SEMICONDUCTOR CORPORATION) 30 November 2006 See abstract, figures 1-13 and claims 1-17.	1-19
A	US 2008-0064168 A1 (NATHAN KRAFT et al.) 13 March 2008 See abstract, figures 1-3 and claims 1-10.	1-19
A	US 5726084 A1 (BOYD; JOHN M. et al.) 10 March 1998 See abstract, figures 1-27 and claims 1-9.	1-19



Further documents are listed in the continuation of Box C.



See patent family annex.

* Special categories of cited documents:

"A" document defining the general state of the art which is not considered to be of particular relevance

"E" earlier application or patent but published on or after the international filing date

"L" document which may throw doubts on priority claim(s) or which is cited to establish the publication date of citation or other special reason (as specified)

"O" document referring to an oral disclosure, use, exhibition or other means

"P" document published prior to the international filing date but later than the priority date claimed

"T" later document published after the international filing date or priority date and not in conflict with the application but cited to understand the principle or theory underlying the invention

"X" document of particular relevance; the claimed invention cannot be considered novel or cannot be considered to involve an inventive step when the document is taken alone

"Y" document of particular relevance; the claimed invention cannot be considered to involve an inventive step when the document is combined with one or more other such documents, such combination being obvious to a person skilled in the art

"&" document member of the same patent family

Date of the actual completion of the international search

17 JUNE 2010 (17.06.2010)

Date of mailing of the international search report

17 JUNE 2010 (17.06.2010)

Name and mailing address of the ISA/KR

Korean Intellectual Property Office
Government Complex-Daejeon, 139 Seonsa-ro, Seo-gu, Daejeon 302-701, Republic of Korea

Facsimile No. 82-42-472-7140

Authorized officer

CHUNG, DOO HAN

Telephone No. 82-42-481-8513



INTERNATIONAL SEARCH REPORT

Information on patent family members

International application No.

PCT/US2009/065856

Patent document cited in search report	Publication date	Patent family member(s)	Publication date
US 2007-0190728 A1	16.08.2007	AT 505375 A2 CN 101379610 A DE 112007000339 T5 JP 2009-526410 A KR 10-2008-0100209 A WO 2007-095438 A3	15.12.2008 04.03.2009 11.12.2008 16.07.2009 14.11.2008 14.02.2008
WO 2006-127914 A2	30.11.2006	AT 504289 A2 CN 101542731 A DE 112006001318 T5 JP 2008-546189 A KR 10-2008-0015863 A	15.04.2008 23.09.2009 17.04.2008 18.12.2008 20.02.2008
US 2008-0064168 A1	13.03.2008	AT 505888 A2 CN 101473443 A DE 112007001454 T5 JP 2009-542002 A KR 10-2009-0018638 A TW 200810113 A WO 2007-149666 A2	15.04.2009 01.07.2009 30.04.2009 26.11.2009 20.02.2009 16.02.2008 27.12.2007
US 5726084 A1	10.03.1998	JP 08-070101 A KR 10-1995-0001935 A	12.03.1996 04.01.1995